



RF360
Europe GmbH

Data sheet

SAW multiplexer

EN-DC 4G/5G band n1 + n66 + n3 + n7

Project:	M5009
Ordering code:	B39272M5009D310
Date:	November 30, 2021
Version:	2.1

DCN: 80-PA243-592 Rev. B

Qualcomm products mentioned herein are products of Qualcomm Technologies, Inc. and/or its subsidiaries.

RF360 Europe GmbH
Anzinger Straße 13
81671 Munich, Germany

© 2021 Qualcomm Technologies, Inc. and/or its subsidiaries. All rights reserved

These materials, including the information contained herein, may be used only for informational purposes by the customer. Qualcomm Technologies, Inc. and/or its subsidiaries assume no responsibility for errors or omissions in these materials or the information contained herein and reserve the right to make changes to the product(s) or information contained herein without notice. The materials and information are provided on an AS IS basis, without warranty, either expressed or implied, with respect to the materials, or any output or results based on the use, application, or evaluation of such materials, including without limitation, with respect to the non-infringement of trademarks, patents, copyrights or any other intellectual property rights or other rights of third parties.

No use of this documentation or any information contained herein grants any license, whether express, implied, by estoppel or otherwise, to any intellectual property rights, including, without limitation, to any patents owned by QUALCOMM Incorporated or any of its subsidiaries.

Not to be used, copied, reproduced, or modified in whole or in part, nor its contents revealed in any manner to others without the express written permission of RF360 Europe GmbH.

Qualcomm is a trademark or registered trademark of Qualcomm Incorporated. Other product and brand names may be trademarks or registered trademarks of their respective owners.

This technical data may be subject to U.S. and international export, re-export, or transfer ("export") laws. Diversion contrary to U.S. and international law is strictly prohibited.

Table of contents

1 [Application](#)..... 4

2 [Features](#)..... 4

3 [Package](#)..... 5

4 [Pin configuration](#)..... 5

5 [Matching circuit](#)..... 6

6 [Characteristics EN-DC 4G/5G n1](#)..... 7

7 [Characteristics EN-DC 4G/5G n3](#)..... 8

8 [Characteristics EN-DC 4G/5G n7](#)..... 11

9 [Characteristics EN-DC 4G/5G n66](#)..... 14

10 [Cross-isolations](#)..... 15

11 [Maximum ratings](#)..... 22

12 [Transmission coefficient EN-DC 4G/5G n1](#)..... 23

13 [Reflection coefficients EN-DC 4G/5G n1](#)..... 24

14 [Transmission coefficients EN-DC 4G/5G n3](#)..... 25

15 [Transmission coefficient \(LTE\) EN-DC 4G/5G n3](#)..... 28

16 [Reflection coefficients EN-DC 4G/5G n3](#)..... 29

17 [Transmission coefficients EN-DC 4G/5G n7](#)..... 30

18 [Transmission coefficient \(WLAN\) EN-DC 4G/5G n7](#)..... 33

19 [Transmission coefficient \(integrated\) EN-DC 4G/5G n7](#)..... 34

20 [Reflection coefficients EN-DC 4G/5G n7](#)..... 35

21 [Transmission coefficient EN-DC 4G/5G n66](#)..... 36

22 [Reflection coefficients EN-DC 4G/5G n66](#)..... 37

23 [Transmission coefficients cross-isolations](#)..... 38

24 [Packing material](#)..... 45

25 [Marking](#)..... 49

26 [Soldering profile](#)..... 50

27 [Annotations](#)..... 51

28 [Cautions and warnings](#)..... 52

29 [Important notes](#)..... 53

1 Application

- Low-loss SAW multiplexer for mobile telephone EN-DC 4G/5G Band n1, Band n66, Band n3 and Band n7 systems.
- EN-DC 4G/5G band n1 uplink: 1950 MHz (pass band 60 MHz)
- EN-DC 4G/5G band n1 downlink: 2140 MHz (pass band 60 MHz)
- EN-DC 4G/5G band n3 uplink: 1747.5 MHz (pass band 75 MHz)
- EN-DC 4G/5G band n3 downlink: 1842.5 MHz (pass band 75 MHz)
- EN-DC 4G/5G band n7 uplink: 2535 MHz (pass band 70 MHz)
- EN-DC 4G/5G band n7 downlink: 2655 MHz (pass band 70 MHz)
- EN-DC 4G/5G band n66 uplink: 1745 MHz (pass band 70 MHz)
- EN-DC 4G/5G band n66 downlink: 2155 MHz (pass band 90 MHz)
- Usable pass bands: 60MHz for Band n1, 70/90MHz for Band n66, 75MHz for Band n3 and 70MHz for Band n7.
- High out of band selectivity
- High TX-RX isolation
- Terminating impedance 50Ω
- Unbalanced to unbalanced operation

2 Features

- Package size 2.5 \pm 0.1 mm × 2.0 \pm 0.1 mm
- Package height 0.65 mm (max.)
- Approximate weight 0.008 g
- RoHS compatible
- Package for Surface Mount Technology (SMT)
- Ni/Au-plated terminals
- Electrostatic Sensitive Device (ESD)
- Moisture Sensitivity Level 3 (MSL3)

5 Matching circuit

- $L_{s1} = 2.4 \text{ nH}$
- $L_{s5} = 3.8 \text{ nH}$
- $L_{s7} = 2.9 \text{ nH}$
- $L_{s9} = 2.1 \text{ nH}$
- $L_{s13} = 1.2 \text{ nH}$
- $L_{s15} = 1.8 \text{ nH}$

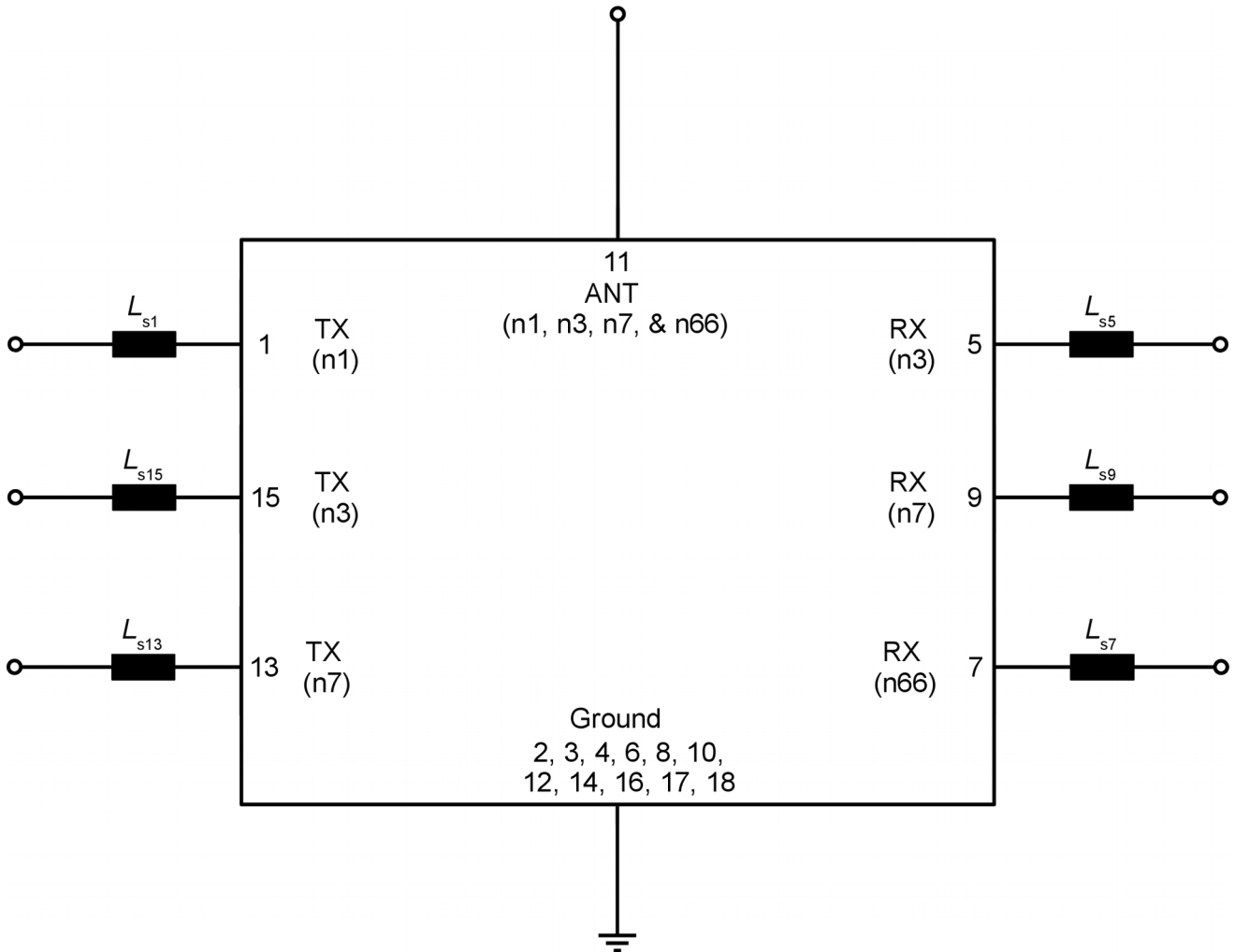


Figure 2: Schematic of matching circuit.

External shunt inductor for ESD protection is recommended at any ports towards antenna.

6 Characteristics EN-DC 4G/5G n1

Temperature range for specification	T_{SPEC}	= -30 °C ... +85 °C
n1 TX terminating impedance	$Z_{n1 TX}$	= 50 Ω + 2.4 nH ¹⁾
ANT terminating impedance	Z_{ANT}	= 50 Ω

Characteristics EN-DC 4G/5G n1 TX – ANT			min. for T_{SPEC}	typ. @ +25 °C	max. for T_{SPEC}	
Maximum insertion attenuation						
	1920... 1980	MHz	—	1.6	2.4	dB
Amplitude ripple (p-p)						
	1920... 1980	MHz	—	0.2	2.0	dB
Maximum VSWR						
@ n1 TX port	1920... 1980	MHz	—	1.6	2.0	
@ ANT port	1920... 1980	MHz	—	1.5	2.0	
Minimum attenuation						
	10... 1574	MHz	40	56	—	dB
	1166... 1187	MHz	44	56	—	dB
	1559... 1606	MHz	43	66	—	dB
	1710... 1785	MHz	40	48	—	dB
	1805... 1880	MHz	45	58	—	dB
	1880... 1895	MHz	10	15	—	dB
	2010... 2025	MHz	20 ³⁾	37	—	dB
	2110... 2200	MHz	45	63	—	dB
	2400... 2500	MHz	40	55	—	dB
	2496... 2690	MHz	45	55	—	dB
	2500... 2570	MHz	40	55	—	dB
	3300... 4200	MHz	40	61	—	dB
	3840... 3960	MHz	40	69	—	dB
	4400... 5000	MHz	40	64	—	dB
	5150... 5925	MHz	40	60	—	dB

¹⁾ See Sec. Matching circuit (p. 6).

²⁾ Over any 5 MHz.

³⁾ Valid for temperature $T = +15$ °C...+85 °C.

7 Characteristics EN-DC 4G/5G n3

7.1 TX – ANT

Temperature range for specification	T_{SPEC}	= -30 °C ... +85 °C
n3 TX terminating impedance	$Z_{n3 TX}$	= 50 Ω + 1.8 nH ¹⁾
ANT terminating impedance	Z_{ANT}	= 50 Ω
n3 RX terminating impedance	$Z_{n3 RX}$	= 50 Ω + 3.8 nH ¹⁾

Characteristics EN-DC 4G/5G n3 TX – ANT			min. for T_{SPEC}	typ. @ +25 °C	max. for T_{SPEC}	
Maximum insertion attenuation		α_{max}				
	1710... 1785	MHz	—	2.1	2.8	dB
Amplitude ripple (p-p)		$\Delta\alpha^{2)}$				
	1710... 1785	MHz	—	0.6	2.0	dB
Maximum VSWR		VSWR _{max}				
@ n3 TX port	1710... 1785	MHz	—	1.5	2.0	
@ ANT port	1710... 1785	MHz	—	1.5	2.0	
Minimum attenuation		α_{min}				
	10... 1566	MHz	40	47	—	dB
	703... 960	MHz	40	48	—	dB
	1166... 1187	MHz	44	47	—	dB
	1559... 1606	MHz	45	60	—	dB
	1805... 1880	MHz	45	61	—	dB
	1920... 1980	MHz	35	42	—	dB
	2110... 2200	MHz	45	62	—	dB
	2400... 2500	MHz	36	40	—	dB
	2496... 2690	MHz	35	41	—	dB
	2500... 2570	MHz	35	41	—	dB
	3300... 4200	MHz	35	54	—	dB
	3420... 3570	MHz	35	54	—	dB
	4400... 5000	MHz	35	54	—	dB
	5130... 5925	MHz	35	53	—	dB

¹⁾ See Sec. Matching circuit (p. 6).

²⁾ Over any 5 MHz.

7.2 ANT – RX

Temperature range for specification	T_{SPEC}	= -30 °C ... +85 °C
n3 TX terminating impedance	$Z_{n3 TX}$	= 50 Ω + 1.8 nH ¹⁾
ANT terminating impedance	Z_{ANT}	= 50 Ω
n3 RX terminating impedance	$Z_{n3 RX}$	= 50 Ω + 3.8 nH ¹⁾

Characteristics EN-DC 4G/5G n3 ANT – RX			min. for T_{SPEC}	typ. @ +25 °C	max. for T_{SPEC}	
Maximum insertion attenuation		α_{max}				
	1805... 1880	MHz	—	2.0	3.3	dB
Amplitude ripple (p-p)		$\Delta\alpha^{2)}$				
	1805... 1880	MHz	—	0.4	2.0	dB
Maximum VSWR		VSWR _{max}				
@ ANT port	1805... 1880	MHz	—	1.5	2.0	
@ n3 RX port	1805... 1880	MHz	—	1.6	2.0	
Minimum attenuation		α_{min}				
	10... 1720	MHz	45	56	—	dB
	95	MHz	50	102	—	dB
	1615... 1690	MHz	40	56	—	dB
	1710... 1785	MHz	45	55	—	dB
	1720... 1755	MHz	12	60	—	dB
	1785... 1790	MHz	10	34	—	dB
	1920... 1980	MHz	45	61	—	dB
	1940... 1965	MHz	12	61	—	dB
	1965... 6000	MHz	25	41	—	dB
	2400... 2500	MHz	35	53	—	dB
	2496... 2690	MHz	38	50	—	dB
	2500... 2570	MHz	45	58	—	dB
	3300... 4200	MHz	35	60	—	dB
	3610... 3760	MHz	35	62	—	dB
	4400... 5000	MHz	35	65	—	dB
	5150... 5925	MHz	35	66	—	dB

¹⁾ See Sec. Matching circuit (p. 6).
²⁾ Over any 5 MHz.

7.3 TX – RX

Temperature range for specification	T_{SPEC}	= -30 °C ... +85 °C
n3 TX terminating impedance	$Z_{n3 TX}$	= 50 Ω + 1.8 nH ¹⁾
ANT terminating impedance	Z_{ANT}	= 50 Ω
n3 RX terminating impedance	$Z_{n3 RX}$	= 50 Ω + 3.8 nH ¹⁾

Characteristics EN-DC 4G/5G n3 TX – RX				min. for T_{SPEC}	typ. @ +25 °C	max. for T_{SPEC}	
Minimum isolation							
	1710... 1785	MHz	$\alpha_{INT,min}^{2)}$	55	62	—	dB
	1805... 1880	MHz	α_{min}	55	64	—	dB

¹⁾ See Sec. Matching circuit (p. 6).

²⁾ Integrated attenuation α_{INT} : Averaged power $|S_{ij}|^2$ over the center 4.5 MHz of LTE 5.0 MHz (25 RB) channels.

8 Characteristics EN-DC 4G/5G n7

8.1 TX – ANT

Temperature range for specification	T_{SPEC}	= -30 °C ... +85 °C
n7 TX terminating impedance	$Z_{n7 TX}$	= 50 Ω + 1.2 nH ¹⁾
ANT terminating impedance	Z_{ANT}	= 50 Ω
n7 RX terminating impedance	$Z_{n7 RX}$	= 50 Ω + 2.1 nH ¹⁾

Characteristics EN-DC 4G/5G n7 TX – ANT				min. for T_{SPEC}	typ. @ +25 °C	max. for T_{SPEC}	
Maximum insertion attenuation							
	2500... 2570	MHz	α_{max}	—	1.8	2.4	dB
Amplitude ripple (p-p)							
	2500... 2570	MHz	$\Delta\alpha^{2)}$	—	0.3	2.0	dB
Maximum VSWR							
			VSWR _{max}				
@ n7 TX port	2500... 2570	MHz		—	1.3	2.0	
@ ANT port	2500... 2570	MHz		—	1.6	2.0	
Minimum attenuation							
	10... 1566	MHz	α_{min}	40	55	—	dB
	1452... 1496	MHz	α_{min}	45	63	—	dB
	1559... 1606	MHz	α_{min}	35	70	—	dB
	1606... 1680	MHz	α_{min}	35	57	—	dB
	1710... 1785	MHz	α_{min}	40	44	—	dB
	1805... 1880	MHz	α_{min}	45	62	—	dB
	1900... 1920	MHz	α_{min}	30	60	—	dB
	1920... 1980	MHz	α_{min}	40	59	—	dB
	2010... 2025	MHz	α_{min}	30	74	—	dB
	2110... 2200	MHz	α_{min}	45	61	—	dB
	2300... 2400	MHz	α_{min}	37	44	—	dB
	2403... 2471	MHz	$\alpha_{WLAN,min}^{3)}$	35	44	—	dB
	2458... 2476	MHz	$\alpha_{WLAN,min}^{3)}$	20	31	—	dB
	2463... 2481	MHz	$\alpha_{WLAN,min}^{3)}$	10	19	—	dB
	2595... 2620	MHz	$\alpha_{min}^{4)}$	12 ⁴⁾	17	—	dB
	2620... 2690	MHz	α_{min}	45	59	—	dB
	3300... 3800	MHz	α_{min}	25	34	—	dB
	3400... 3600	MHz	α_{min}	35	47	—	dB
	5000... 5140	MHz	α_{min}	30	37	—	dB
	5150... 5925	MHz	α_{min}	32	35	—	dB

1) See Sec. Matching circuit (p. 6).
 2) Over any 5 MHz.
 3) Average over each WLAN channel with band width of 18 MHz.
 4) Valid for temperature $T = +25\text{ °C} \dots +85\text{ °C}$.

8.2 ANT – RX

Temperature range for specification
n7 TX terminating impedance
ANT terminating impedance
n7 RX terminating impedance

$T_{SPEC} = -30\text{ °C} \dots +85\text{ °C}$
 $Z_{n7\text{ TX}} = 50\ \Omega + 1.2\text{ nH}^{1)}$
 $Z_{ANT} = 50\ \Omega$
 $Z_{n7\text{ RX}} = 50\ \Omega + 2.1\text{ nH}^{1)}$

Characteristics EN-DC 4G/5G n7 ANT – RX				min. for T_{SPEC}	typ. @ +25 °C	max. for T_{SPEC}	
Maximum insertion attenuation			α_{max}				
	2620... 2690	MHz		—	1.8	2.6	dB
Amplitude ripple (p-p)			$\Delta\alpha^{2)}$				
	2620... 2690	MHz		—	0.3	2.0	dB
Maximum VSWR			VSWR _{max}				
@ ANT port	2620... 2690	MHz		—	1.5	2.0	
@ n7 RX port	2620... 2690	MHz		—	1.3	2.0	
Minimum attenuation							
	1.0... 2500	MHz	α_{min}	40	43	—	dB
	40... 50	MHz	α_{min}	50	103	—	dB
	880... 915	MHz	α_{min}	45	57	—	dB
	1310... 1345	MHz	α_{min}	40	59	—	dB
	1710... 1785	MHz	α_{min}	45	58	—	dB
	1920... 1980	MHz	α_{min}	45	58	—	dB
	2400... 2480	MHz	α_{min}	40	58	—	dB
	2500... 2570	MHz	α_{min}	45	56	—	dB
	2750... 2775	MHz	α_{min}	18	72	—	dB
	2775... 3300	MHz	α_{min}	40	54	—	dB
	3300... 3800	MHz	$\alpha_{INT,min}^{3)}$	32	51	—	dB
	3800... 4200	MHz	$\alpha_{INT,min}^{3)}$	30	34	—	dB
	4200... 6000	MHz	α_{min}	40	51	—	dB
	5150... 5925	MHz	α_{min}	40	51	—	dB

¹⁾ See Sec. Matching circuit (p. 6).

²⁾ Over any 5 MHz.

³⁾ Integrated over 10 MHz.

8.3 TX – RX

Temperature range for specification
n7 TX terminating impedance
ANT terminating impedance
n7 RX terminating impedance

$T_{SPEC} = -30\text{ °C} \dots +85\text{ °C}$
 $Z_{n7\text{ TX}} = 50\ \Omega + 1.2\text{ nH}^{1)}$
 $Z_{ANT} = 50\ \Omega$
 $Z_{n7\text{ RX}} = 50\ \Omega + 2.1\text{ nH}^{1)}$

Characteristics EN-DC 4G/5G n7 TX – RX		min. for T_{SPEC}	typ. @ +25 °C	max. for T_{SPEC}	
Minimum isolation	α_{min}				
	2500... 2570 MHz	55	60	—	dB
	2620... 2690 MHz	55	61	—	dB

¹⁾ See Sec. Matching circuit (p. 6).

9 Characteristics EN-DC 4G/5G n66

Temperature range for specification $T_{SPEC} = -30\text{ °C} \dots +85\text{ °C}$
 ANT terminating impedance $Z_{ANT} = 50\ \Omega$
 n66 RX terminating impedance $Z_{n66\text{ RX}} = 50\ \Omega + 2.9\text{ nH}^1)$

Characteristics EN-DC 4G/5G n66 ANT – RX			min. for T_{SPEC}	typ. @ +25 °C	max. for T_{SPEC}	
Maximum insertion attenuation						
	2110... 2200	MHz	—	1.8	2.4	dB
Amplitude ripple (p-p)						
	2110... 2200	MHz	—	0.3	1.5	dB
Maximum VSWR						
@ ANT port	2110... 2200	MHz	—	1.4	2.0	
@ n66 RX port	2110... 2200	MHz	—	1.4	2.0	
Minimum attenuation						
	10... 2025	MHz	40	43	—	dB
	190	MHz	50	90	—	dB
	699... 748	MHz	40	66	—	dB
	1055... 1085	MHz	48	61	—	dB
	1710... 1785	MHz	45	61	—	dB
	1730... 1790	MHz	40	61	—	dB
	1920... 1980	MHz	45	63	—	dB
	2015... 2025	MHz	37	52	—	dB
	2025... 2050	MHz	22	57	—	dB
	2050... 2075	MHz	8	40	—	dB
	2230... 2255	MHz	12	53	—	dB
	2255... 6000	MHz	25	42	—	dB
	2400... 2500	MHz	38	63	—	dB
	2500... 2570	MHz	45	60	—	dB
	3300... 4200	MHz	38	60	—	dB
	4030... 4150	MHz	40	61	—	dB
	4220... 4340	MHz	35	64	—	dB
	4400... 5500	MHz	35	64	—	dB
	5150... 5950	MHz	35	65	—	dB
	5950... 6000	MHz	35	67	—	dB

¹⁾ See Sec. Matching circuit (p. 6).

²⁾ Over any 5 MHz.

10 Cross-isolations

10.1 EN-DC 4G/5G n1 TX – n3 RX

Temperature range for specification	T_{SPEC}	= -30 °C ... +85 °C
n1 TX terminating impedance	$Z_{n1 TX}$	= 50 Ω + 2.4 nH ¹⁾
n3 RX terminating impedance	$Z_{n3 RX}$	= 50 Ω + 3.8 nH ¹⁾

Characteristics cross-isolation EN-DC 4G/5G n1 TX – n3 RX			min. for T_{SPEC}	typ. @ +25 °C	max. for T_{SPEC}	
Minimum cross-isolation						
		α_{min}				
	1805... 1880	MHz	55	60	—	dB
	1920... 1980	MHz	55	61	—	dB

¹⁾ See Sec. Matching circuit (p. 6).

10.2 EN-DC 4G/5G n1 TX – n7 RX

Temperature range for specification	T_{SPEC}	= -30 °C ... +85 °C
n1 TX terminating impedance	$Z_{n1 TX}$	= 50 Ω + 2.4 nH ¹⁾
n7 RX terminating impedance	$Z_{n7 RX}$	= 50 Ω + 2.1 nH ¹⁾

Characteristics cross-isolation EN-DC 4G/5G n1 TX – n7 RX			min. for T_{SPEC}	typ. @ +25 °C	max. for T_{SPEC}	
Minimum cross-isolation	α_{min}	1920... 1980 MHz	53	58	—	dB
		2620... 2690 MHz	55	62	—	dB

¹⁾ See Sec. Matching circuit (p. 6).

10.3 EN-DC 4G/5G n1 TX – n66 RX

Temperature range for specification $T_{SPEC} = -30\text{ °C} \dots +85\text{ °C}$
 n1 TX terminating impedance $Z_{n1\text{ TX}} = 50\ \Omega + 2.4\text{ nH}^{1)}$
 n66 RX terminating impedance $Z_{n66\text{ RX}} = 50\ \Omega + 2.9\text{ nH}^{1)}$

Characteristics cross-isolation EN-DC 4G/5G n1 TX – n66 RX			min. for T_{SPEC}	typ. @ +25 °C	max. for T_{SPEC}	
Minimum cross-isolation						
	α_{min}					
		1574... 1577 MHz	40	74	—	dB
		1920... 1980 MHz	55	64	—	dB
		2110... 2200 MHz	55	64	—	dB
		3830... 3970 MHz	30	70	—	dB
		5750... 5950 MHz	30	73	—	dB

¹⁾ See Sec. Matching circuit (p. 6).

10.4 EN-DC 4G/5G n3 TX – n7 RX

Temperature range for specification	T_{SPEC}	= -30 °C ... +85 °C
n3 TX terminating impedance	$Z_{n3 TX}$	= 50 Ω + 1.8 nH ¹⁾
n7 RX terminating impedance	$Z_{n7 RX}$	= 50 Ω + 2.1 nH ¹⁾

Characteristics cross-isolation EN-DC 4G/5G n3 TX – n7 RX			min. for T_{SPEC}	typ. @ +25 °C	max. for T_{SPEC}	
Minimum cross-isolation						
		α_{min}				
	1710... 1785	MHz	55	59	—	dB
	2620... 2690	MHz	55	61	—	dB

¹⁾ See Sec. Matching circuit (p. 6).

10.5 EN-DC 4G/5G n3 TX – n66 RX

Temperature range for specification	T_{SPEC}	= -30 °C ... +85 °C
n3 TX terminating impedance	$Z_{n3 TX}$	= 50 Ω + 1.8 nH ¹⁾
n66 RX terminating impedance	$Z_{n66 RX}$	= 50 Ω + 2.9 nH ¹⁾

Characteristics cross-isolation EN-DC 4G/5G n3 TX – n66 RX			min. for T_{SPEC}	typ. @ +25 °C	max. for T_{SPEC}	
Minimum cross-isolation						
		α_{min}				
	1710... 1785	MHz	55	63	—	dB
	2110... 2200	MHz	55	62	—	dB

¹⁾ See Sec. Matching circuit (p. 6).

10.6 EN-DC 4G/5G n7 TX – n3 RX

Temperature range for specification	T_{SPEC}	= -30 °C ... +85 °C
n7 TX terminating impedance	$Z_{n7 TX}$	= 50 Ω + 1.2 nH ¹⁾
n3 RX terminating impedance	$Z_{n3 RX}$	= 50 Ω + 3.8 nH ¹⁾

Characteristics cross-isolation EN-DC 4G/5G n7 TX – n3 RX			min. for T_{SPEC}	typ. @ +25 °C	max. for T_{SPEC}	
Minimum cross-isolation	α_{min}	1805... 1880 MHz	55	64	—	dB
		2500... 2570 MHz	53	57	—	dB

¹⁾ See Sec. Matching circuit (p. 6).

10.7 EN-DC 4G/5G n7 TX – n66 RX

Temperature range for specification	T_{SPEC}	= -30 °C ... +85 °C
n7 TX terminating impedance	$Z_{n7 TX}$	= 50 Ω + 1.2 nH ¹⁾
n66 RX terminating impedance	$Z_{n66 RX}$	= 50 Ω + 2.9 nH ¹⁾

Characteristics cross-isolation EN-DC 4G/5G n7 TX – EN-DC 4G/5G n66 RX			min. for T_{SPEC}	typ. @ +25 °C	max. for T_{SPEC}	
Minimum cross-isolation	α_{min}	2110... 2200 MHz	55	60	—	dB
		2500... 2570 MHz	55	59	—	dB

¹⁾ See Sec. Matching circuit (p. 6).

11 Maximum ratings

Storage temperature	$T_{STG}^{1)}$ = -40 °C ... +85 °C	
DC voltage	$ V_{DC} ^{2)}$ = 0 V (max.)	
ESD voltage	$V_{ESD}^{3)}$ = 225 V (max.)	Human body model.
Input power	P_{IN}	
@ n1 TX port: 1920 ... 1980 MHz	30 dBm	Continuous wave for 5000 h @ 50 °C. 5 MHz LTE uplink signal (1 RB) for 5000 h @ 50 °C. 5 MHz 5G NR (DFT-s-OFDM) (1 RB) for 5000 h @ 50 °C.
@ n1 TX port: 1920 ... 1980 MHz	28.5 dBm	5 MHz 5G NR (CP-OFDM) (1 RB) for 5000 h @ 50 °C.
@ n3 TX port: 1710 ... 1785 MHz	30 dBm	Continuous wave for 5000 h @ 50 °C. 5 MHz LTE uplink signal (1 RB) for 5000 h @ 50 °C. 5 MHz 5G NR (DFT-s-OFDM) (1 RB) for 5000 h @ 50 °C.
@ n3 TX port: 1710 ... 1785 MHz	28.5 dBm	5 MHz 5G NR (CP-OFDM) (1 RB) for 5000 h @ 50 °C.
@ n7 TX port: 2500 ... 2570 MHz	30 dBm	Continuous wave for 5000 h @ 50 °C. 5 MHz LTE uplink signal (1 RB) for 5000 h @ 50 °C. 5 MHz 5G NR (DFT-s-OFDM) (1 RB) for 5000 h @ 50 °C.
@ n7 TX port: 2500 ... 2570 MHz	28.5 dBm	5 MHz 5G NR (CP-OFDM) (1 RB) for 5000 h @ 50 °C.

¹⁾ Not valid for packaging material. Storage temperature for packaging material is -25 °C to +40 °C.

²⁾ In case of applied DC voltage blocking capacitors are mandatory.

³⁾ According to JESD22-A114F (HBM – Human Body Model), 1 negative & 1 positive pulse.

12 Transmission coefficient EN-DC 4G/5G n1

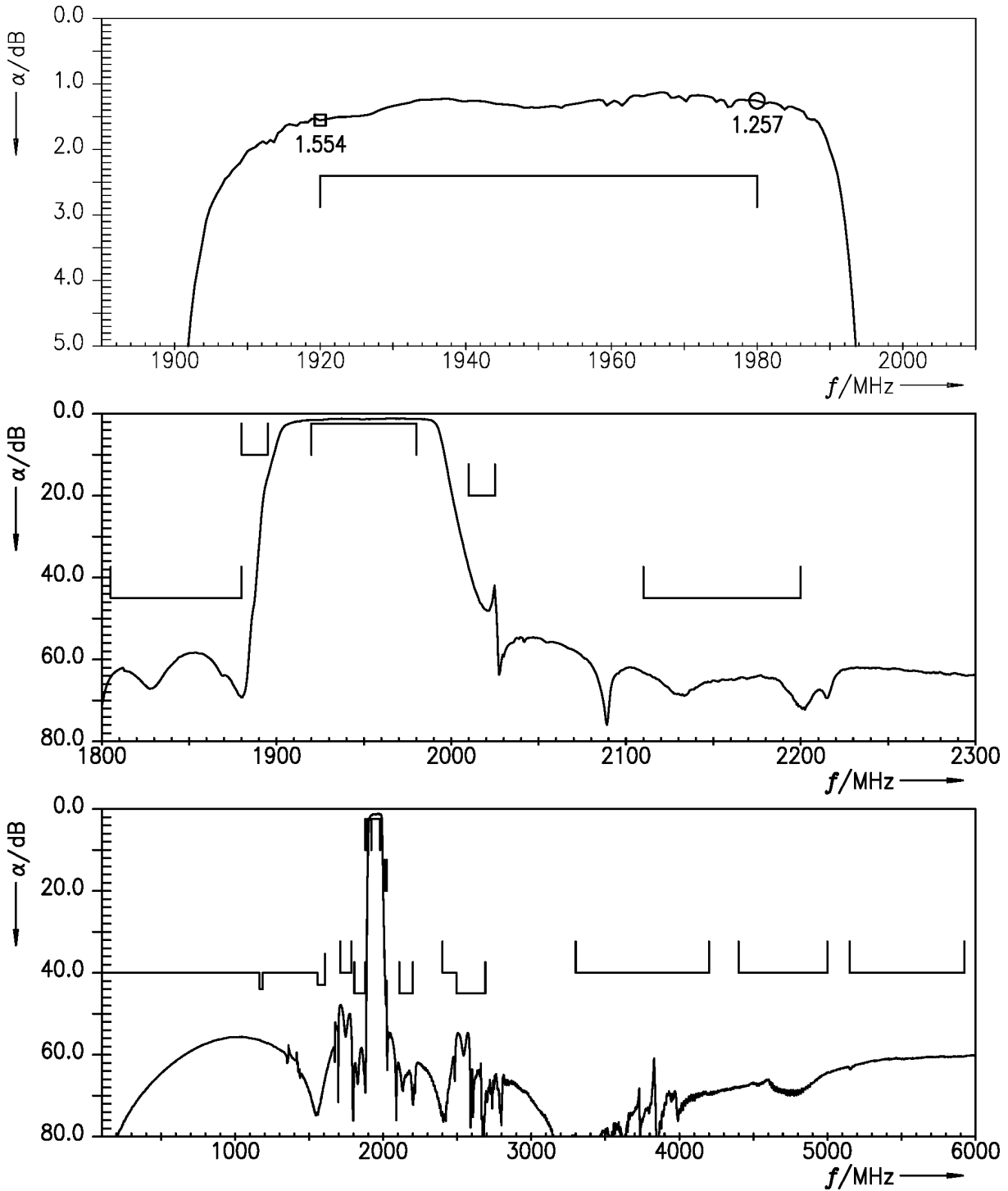


Figure 3: Attenuation TX – ANT.

13 Reflection coefficients EN-DC 4G/5G n1

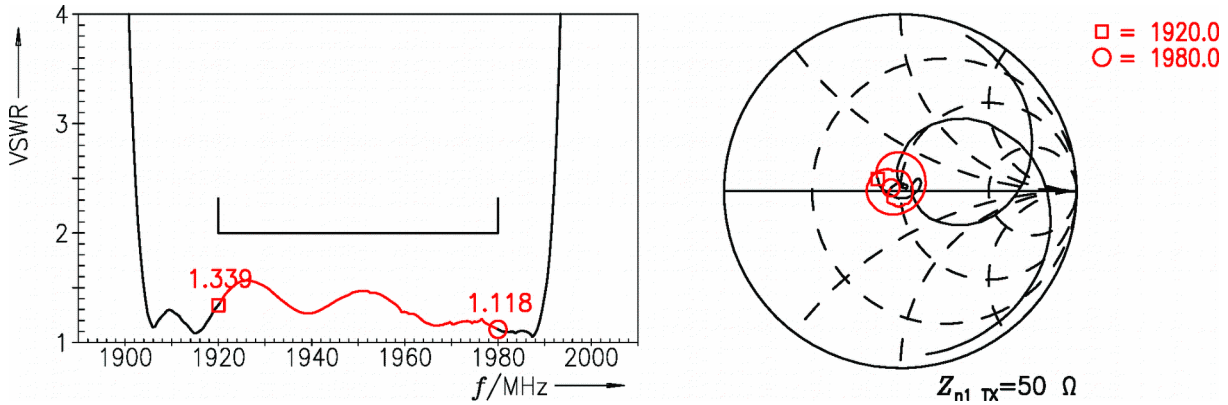


Figure 4: Reflection coefficient at n1 TX port.

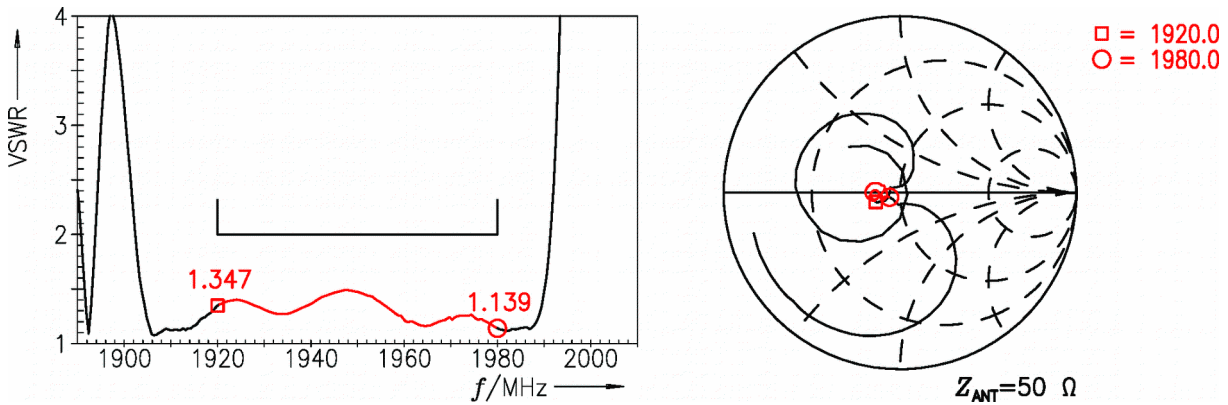


Figure 5: Reflection coefficient at ANT port (TX frequencies).

14 Transmission coefficients EN-DC 4G/5G n3

14.1 TX – ANT

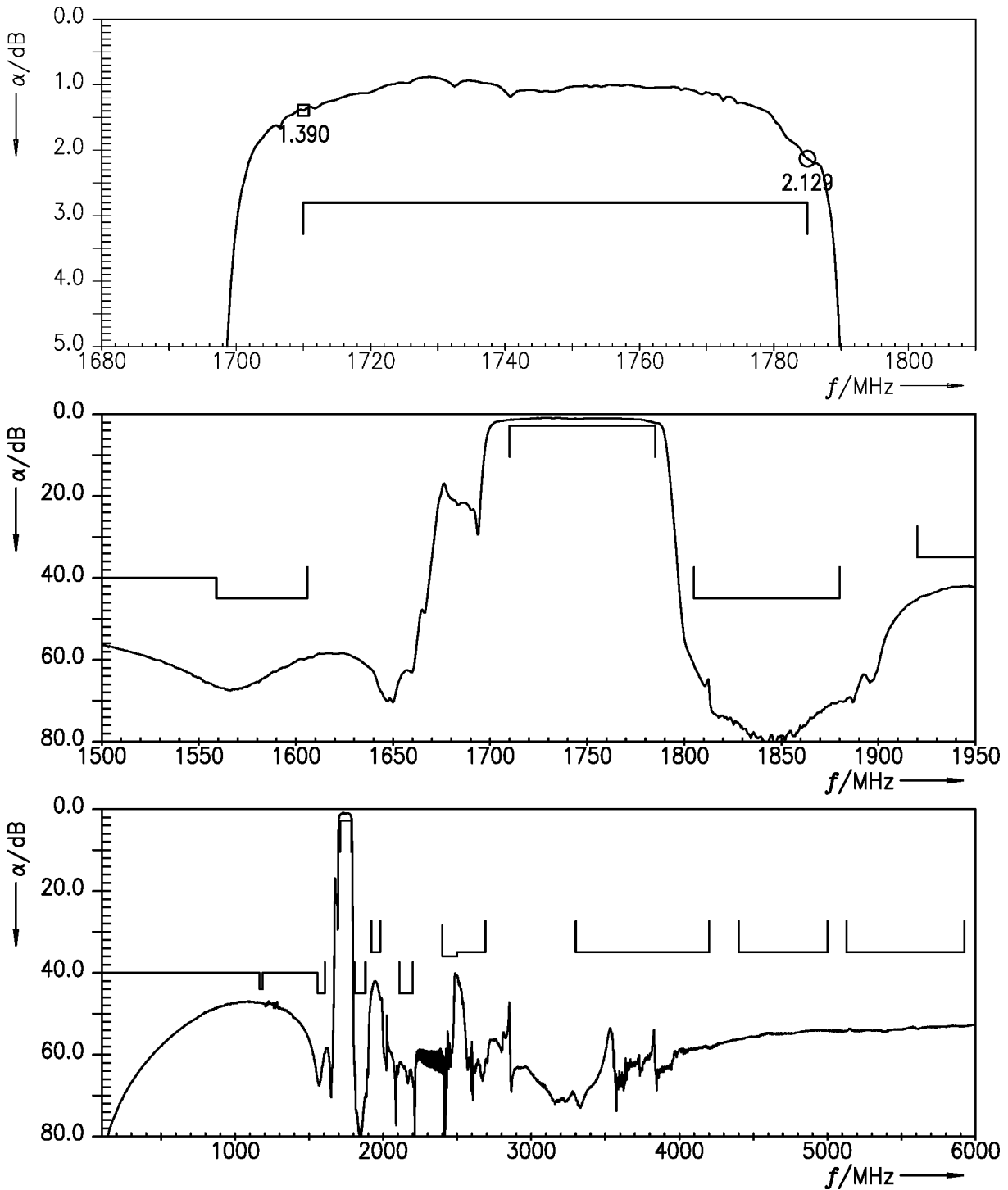


Figure 6: Attenuation TX – ANT.

14.2 ANT – RX

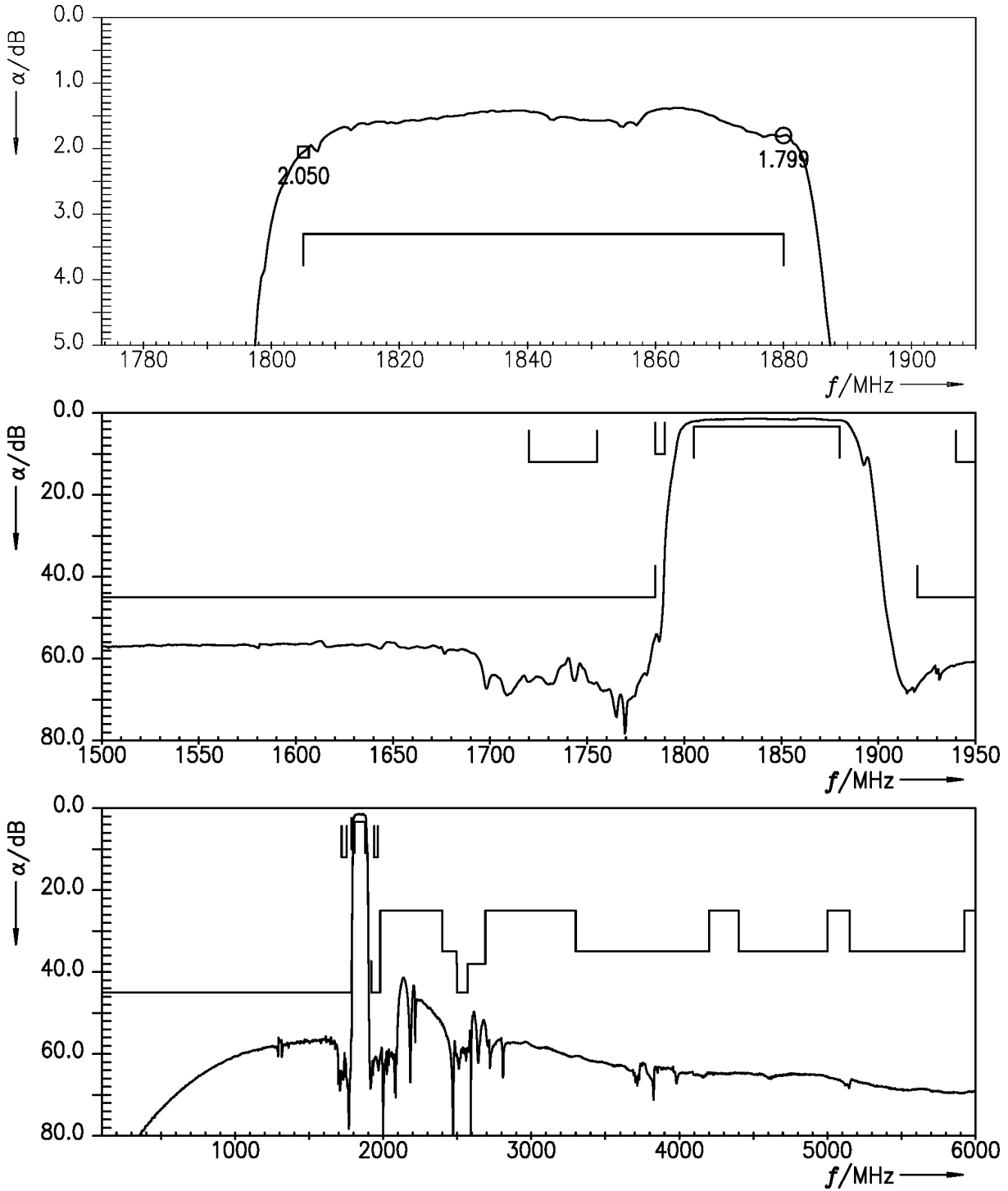


Figure 7: Attenuation ANT – RX.

14.3 TX – RX

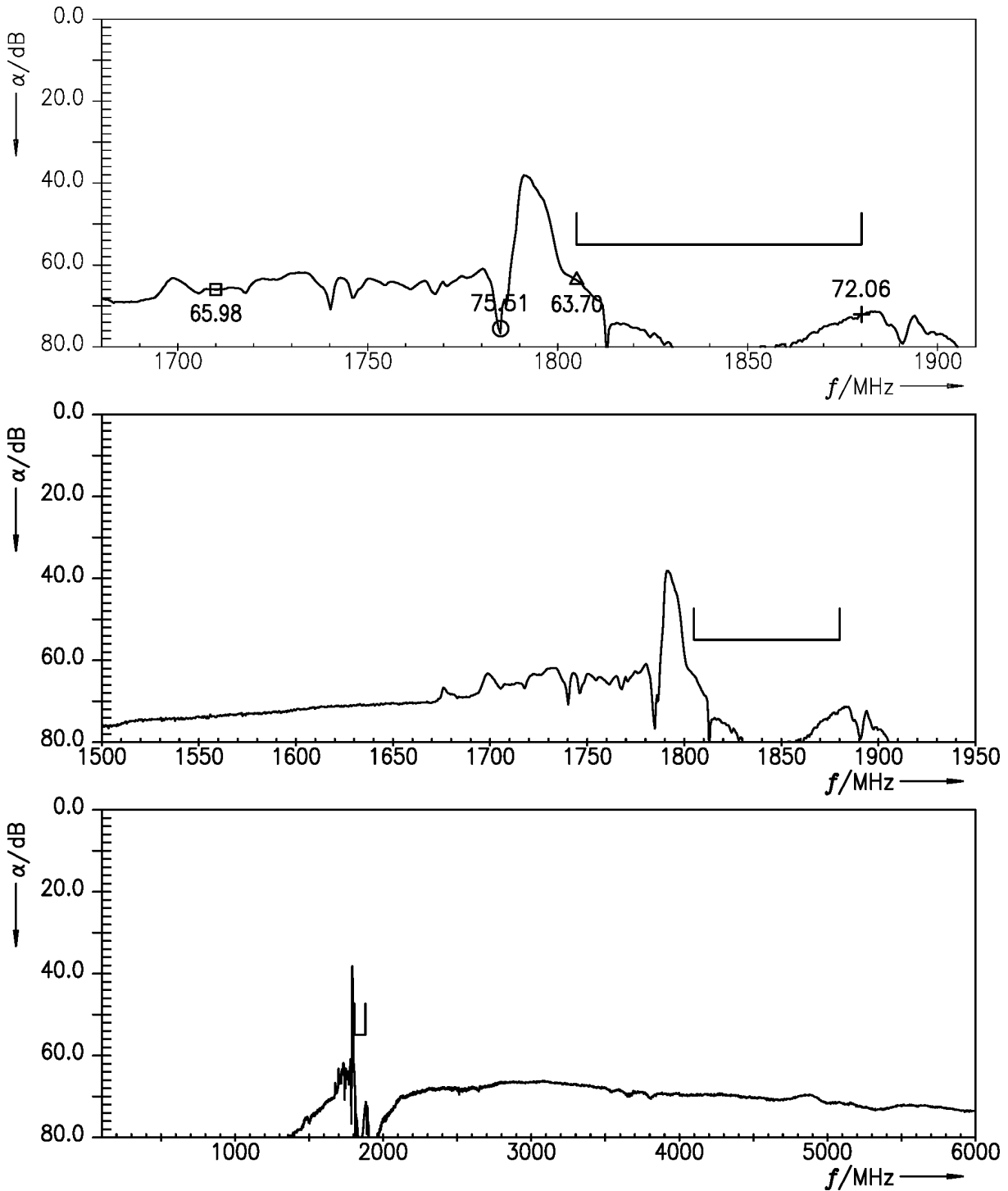


Figure 8: Isolation TX – RX.

15 Transmission coefficient (LTE) EN-DC 4G/5G n3

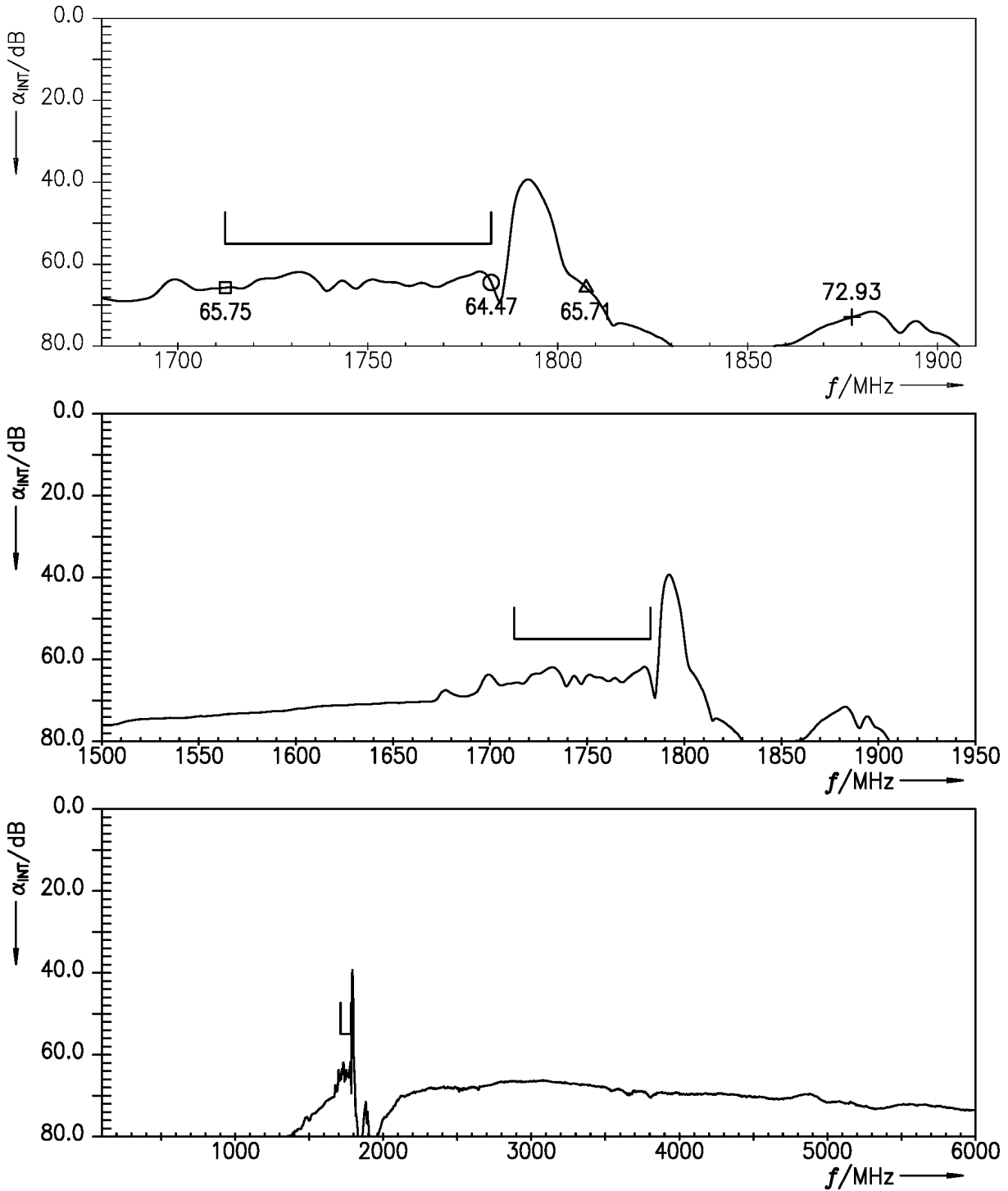


Figure 9: Isolation (LTE) (integration window = 5.0 MHz) TX – RX.

16 Reflection coefficients EN-DC 4G/5G n3

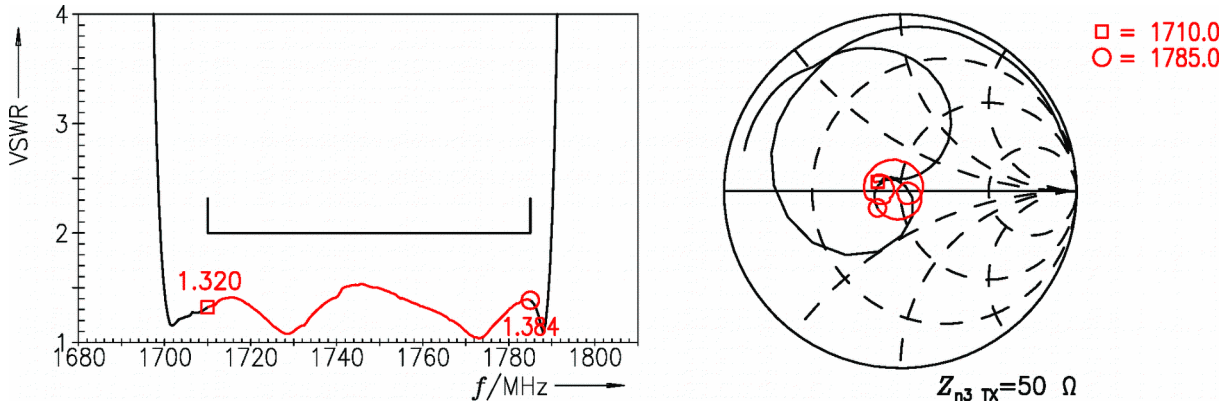


Figure 10: Reflection coefficient at n3 TX port.

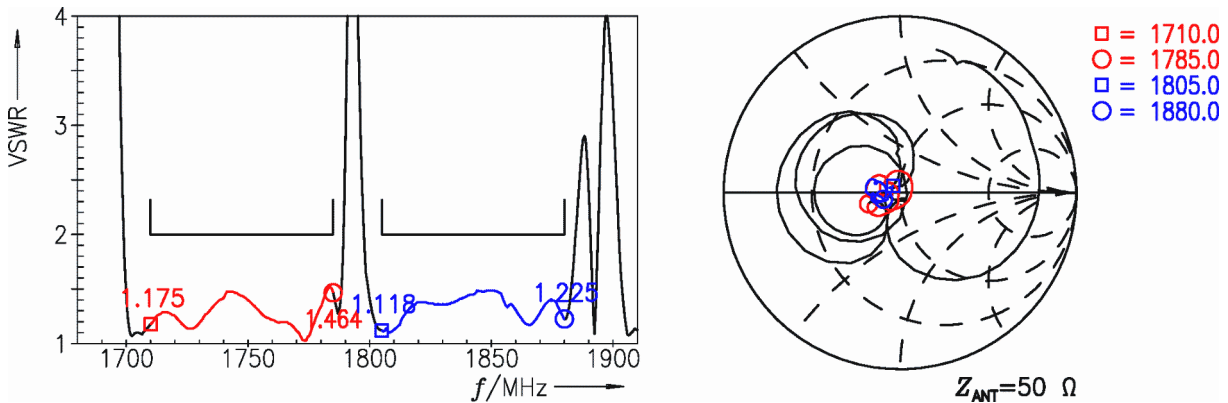


Figure 11: Reflection coefficient at ANT port (TX and RX frequencies).

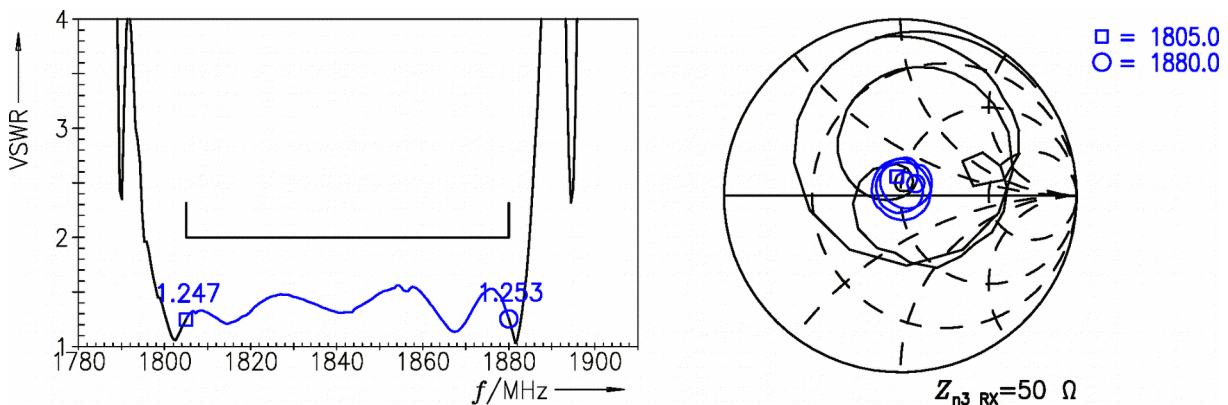


Figure 12: Reflection coefficient at n3 RX port.

17 Transmission coefficients EN-DC 4G/5G n7

17.1 TX – ANT

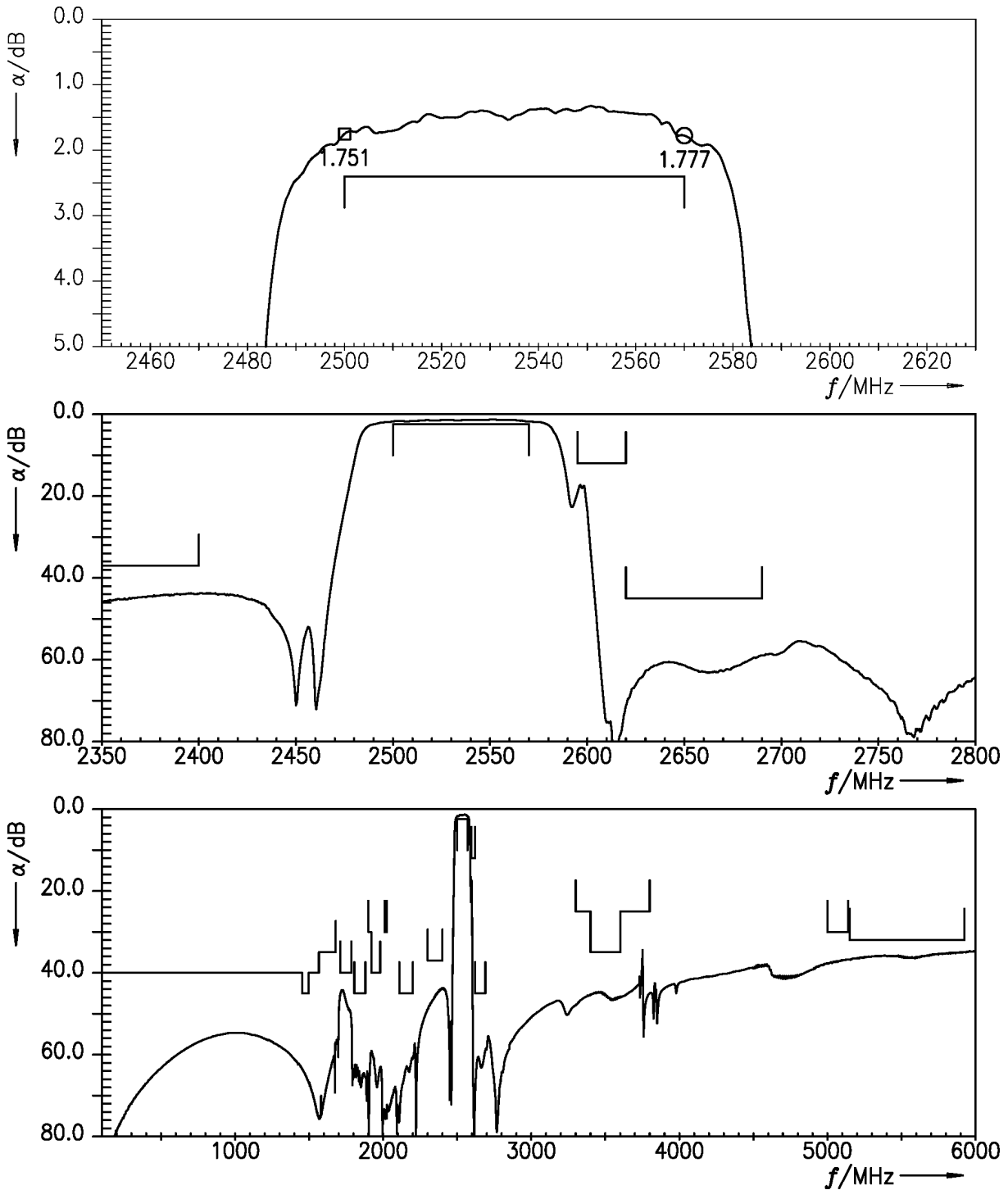


Figure 13: Attenuation TX – ANT.

17.2 ANT – RX

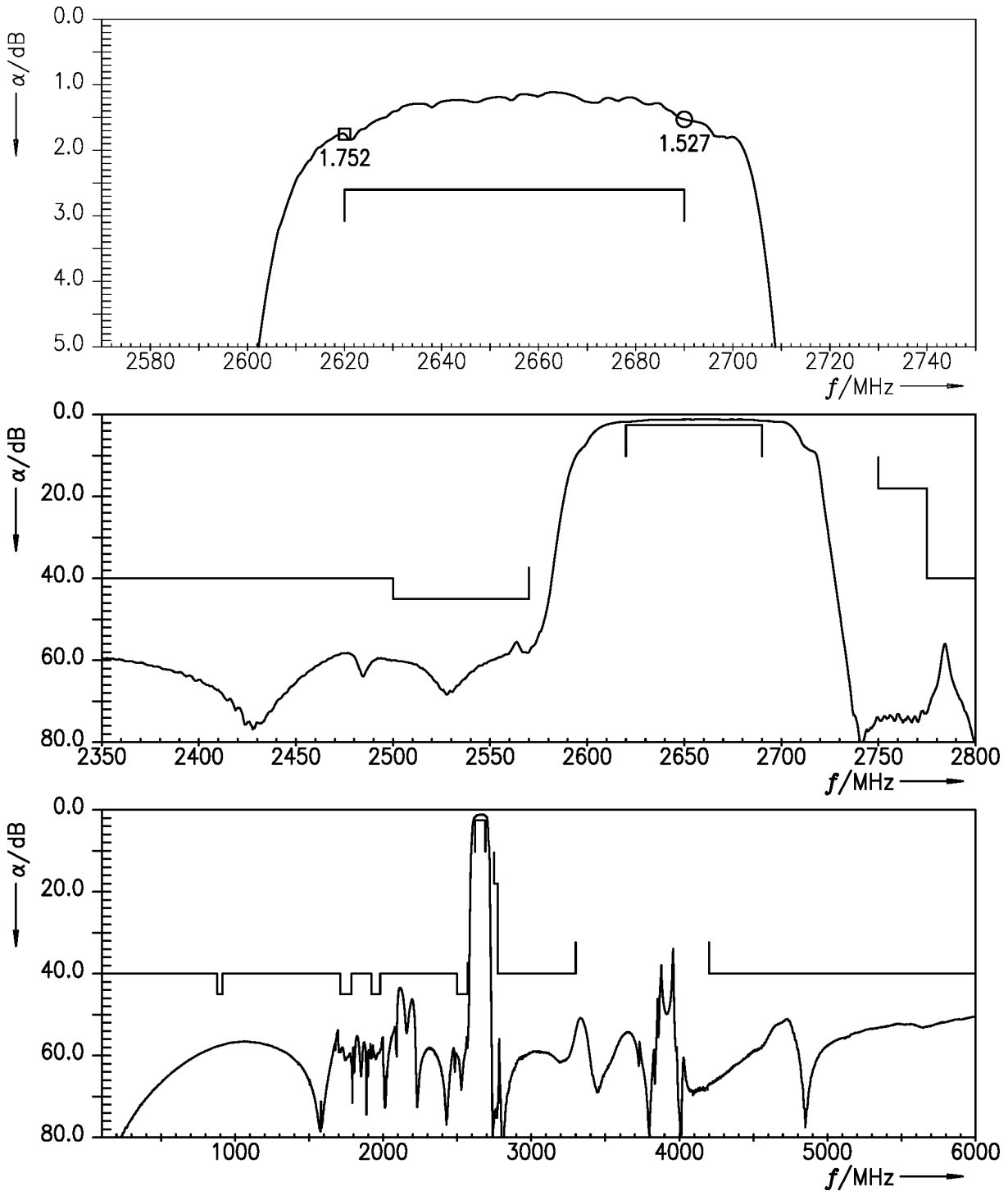


Figure 14: Attenuation ANT – RX.

17.3 TX – RX

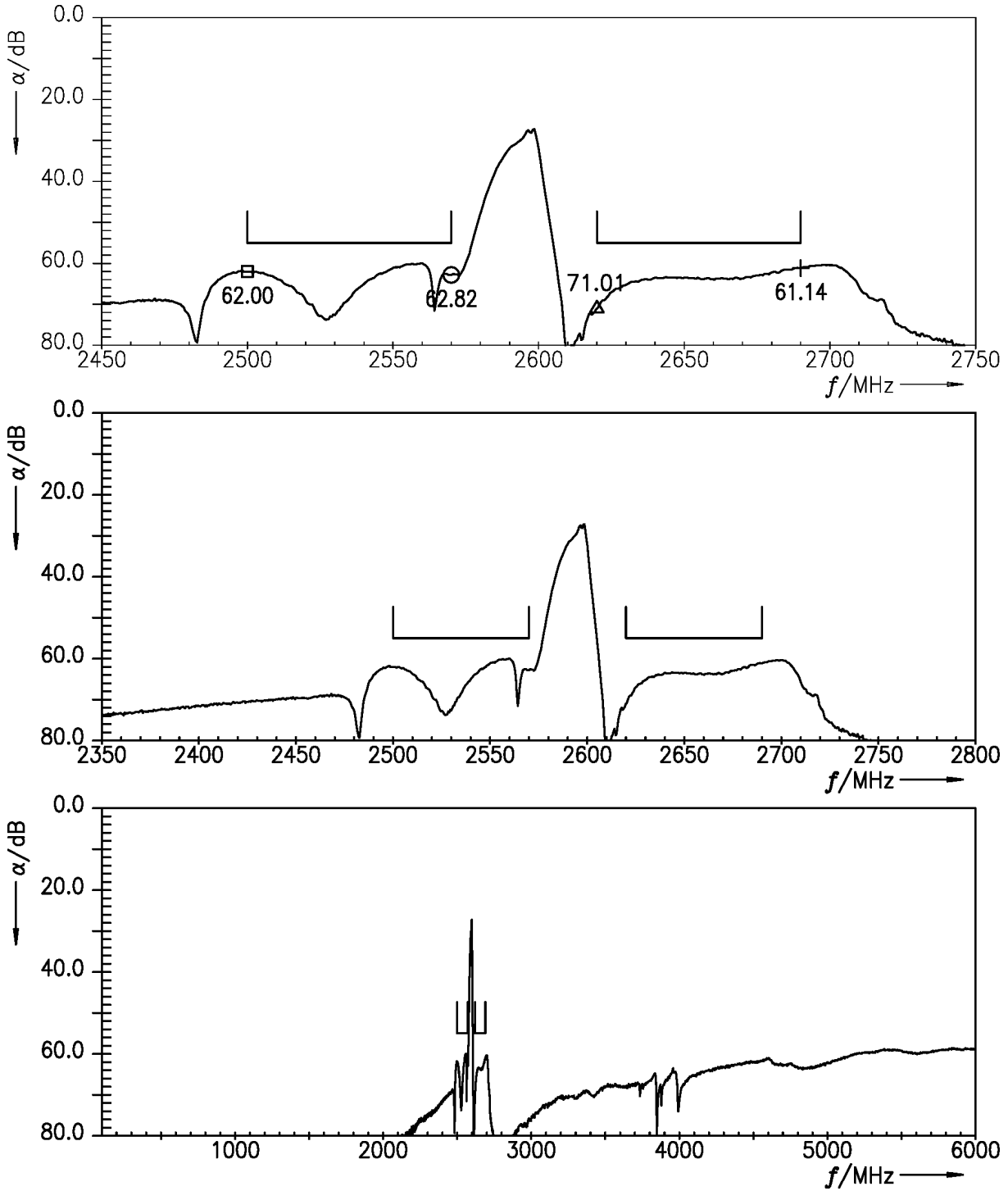


Figure 15: Isolation TX – RX.

18 Transmission coefficient (WLAN) EN-DC 4G/5G n7

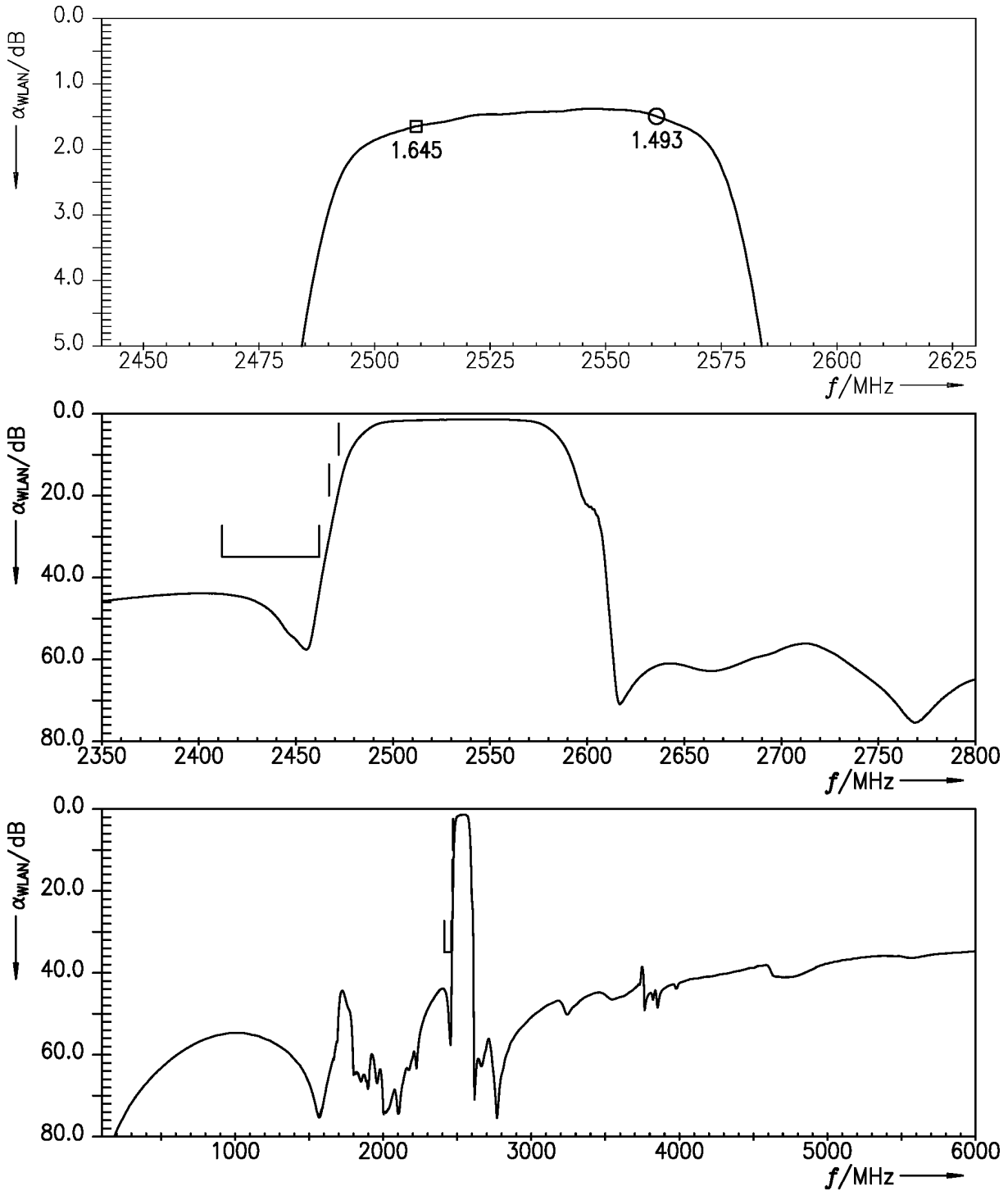


Figure 16: Attenuation (WLAN) (integration window = 18 MHz) TX – ANT.

19 Transmission coefficient (integrated) EN-DC 4G/5G n7

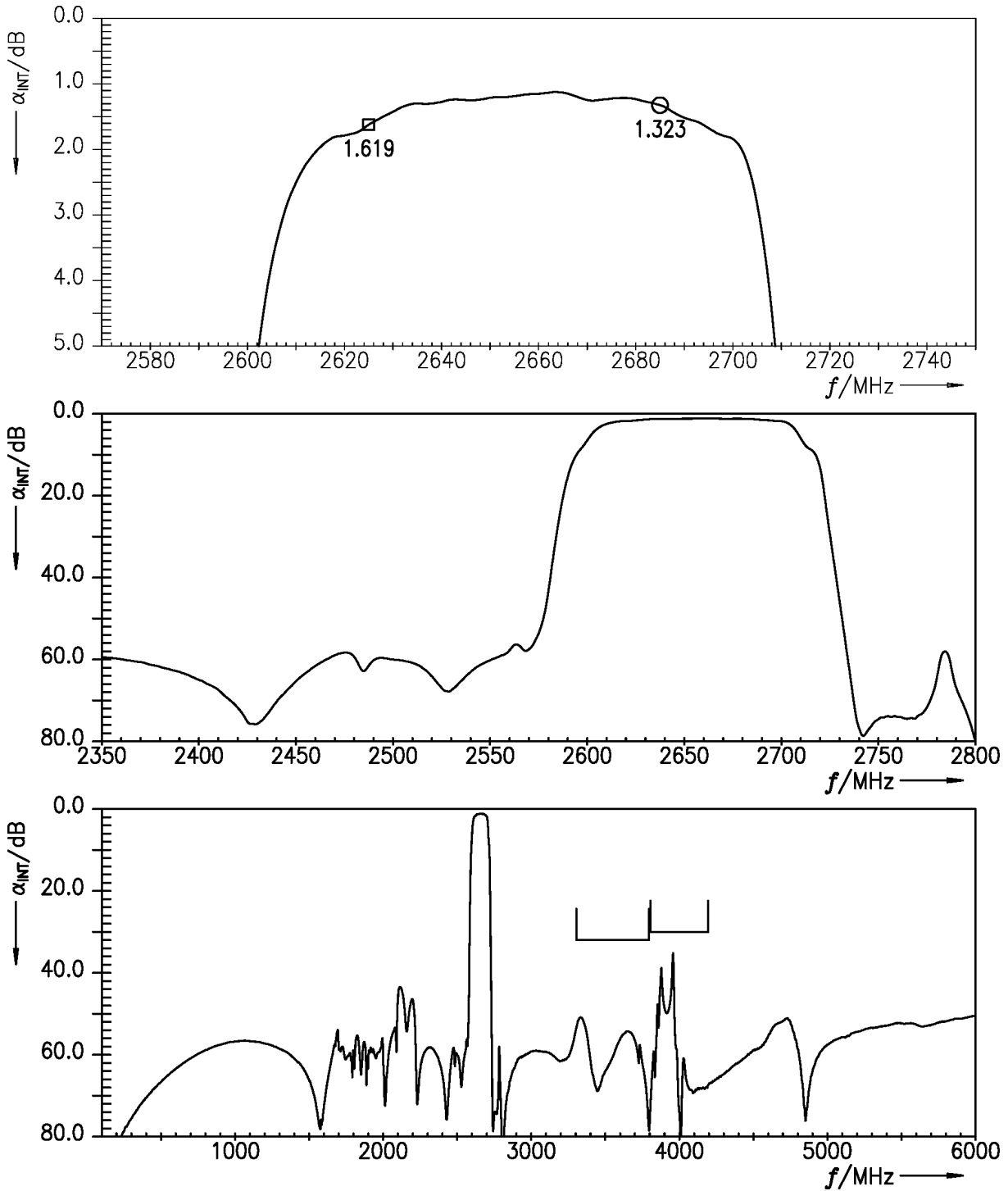


Figure 17: Integrated attenuation (integration window = 10 MHz) ANT – RX.

20 Reflection coefficients EN-DC 4G/5G n7

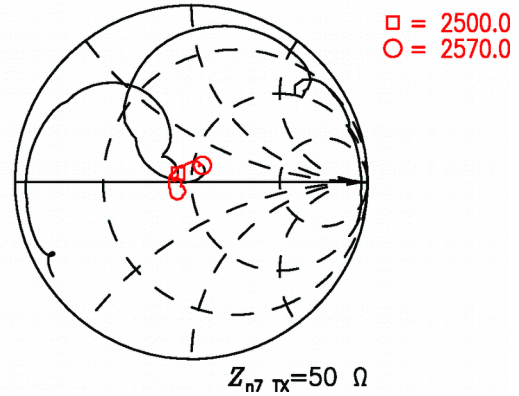
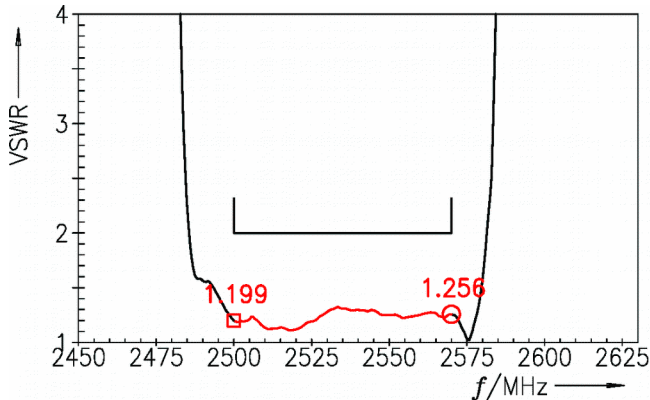


Figure 18: Reflection coefficient at n7 TX port.

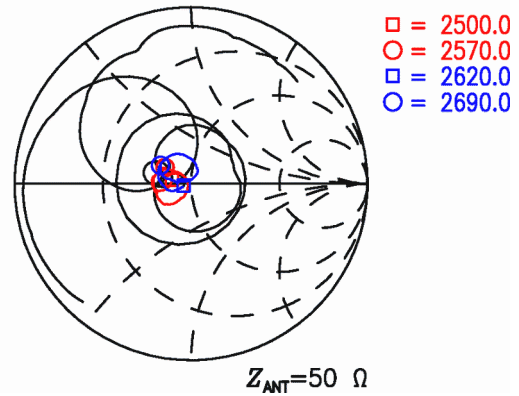
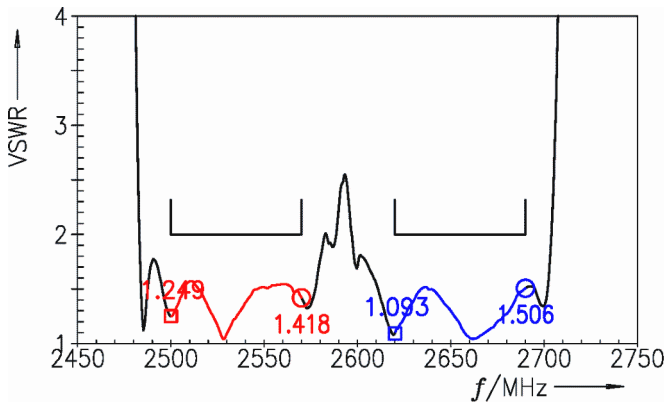


Figure 19: Reflection coefficient at ANT port (TX and RX frequencies).

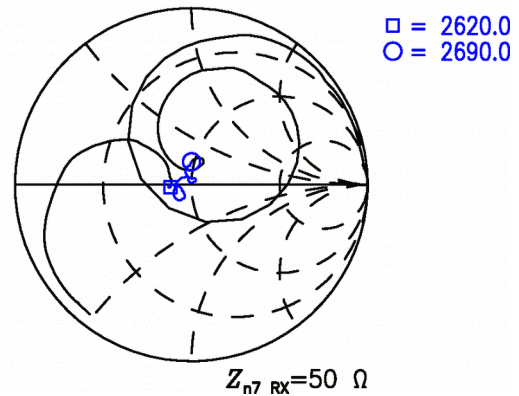
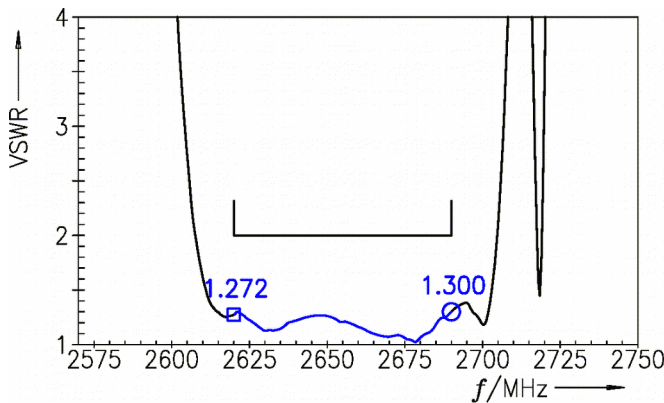


Figure 20: Reflection coefficient at n7 RX port.

21 Transmission coefficient EN-DC 4G/5G n66

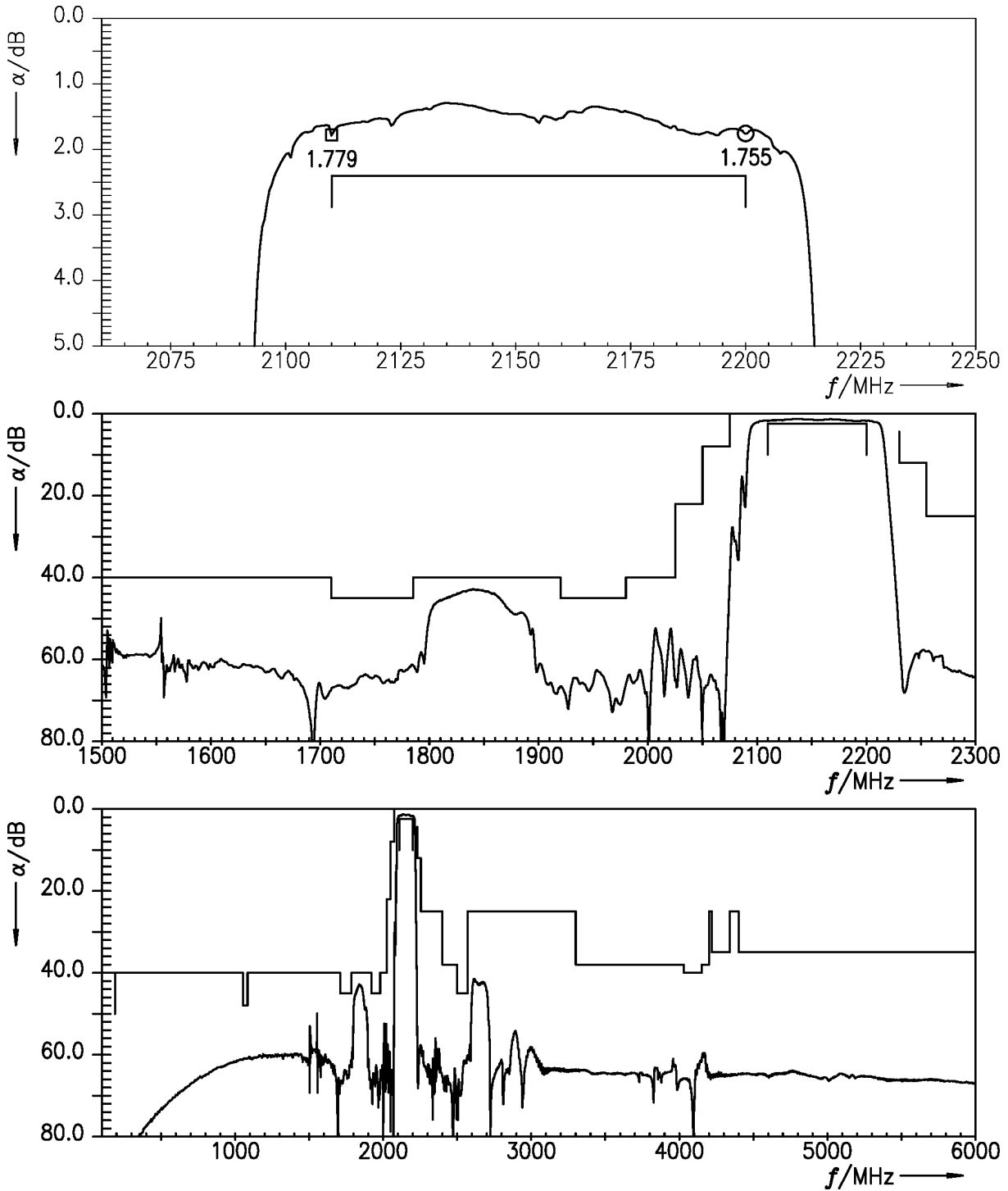


Figure 21: Attenuation ANT – RX.

22 Reflection coefficients EN-DC 4G/5G n66

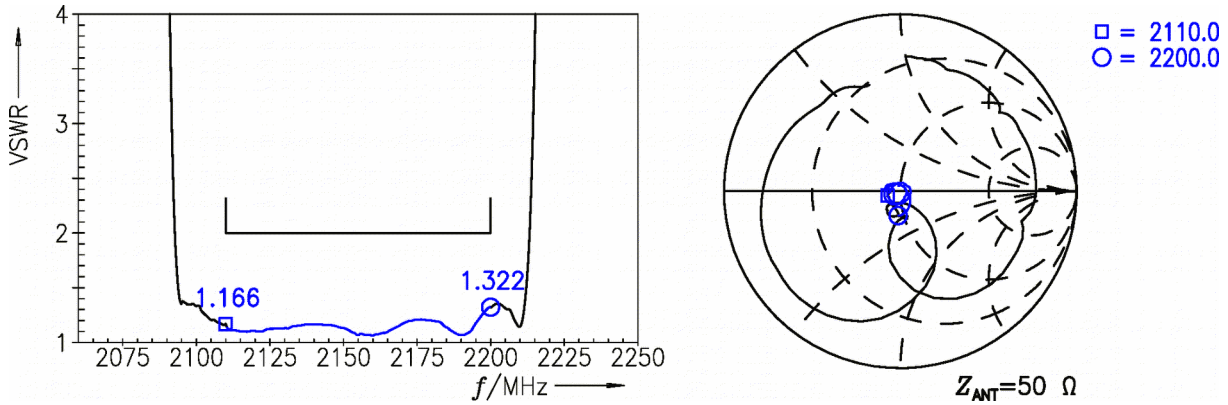


Figure 22: Reflection coefficient at ANT port (RX frequencies).

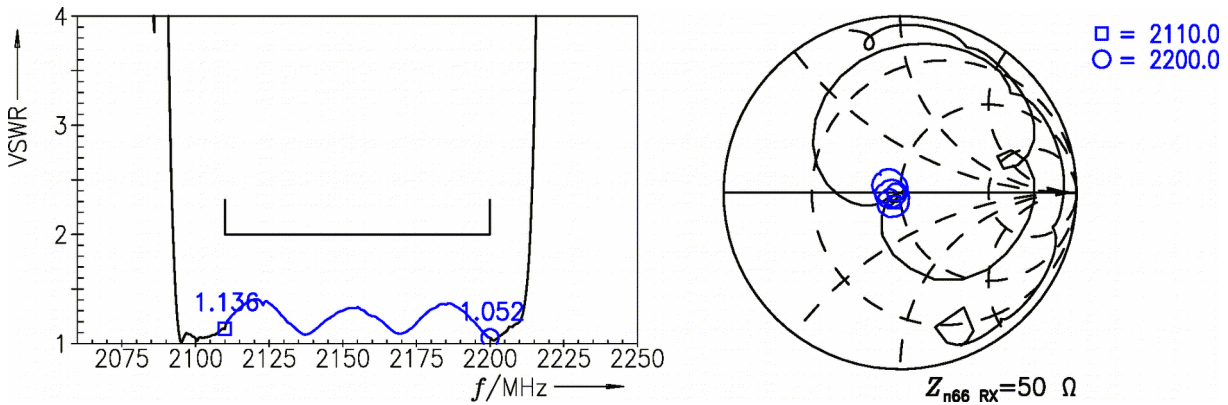


Figure 23: Reflection coefficient at n66 RX port.

23 Transmission coefficients cross-isolations

23.1 EN-DC 4G/5G n1 TX – EN-DC 4G/5G n3 RX

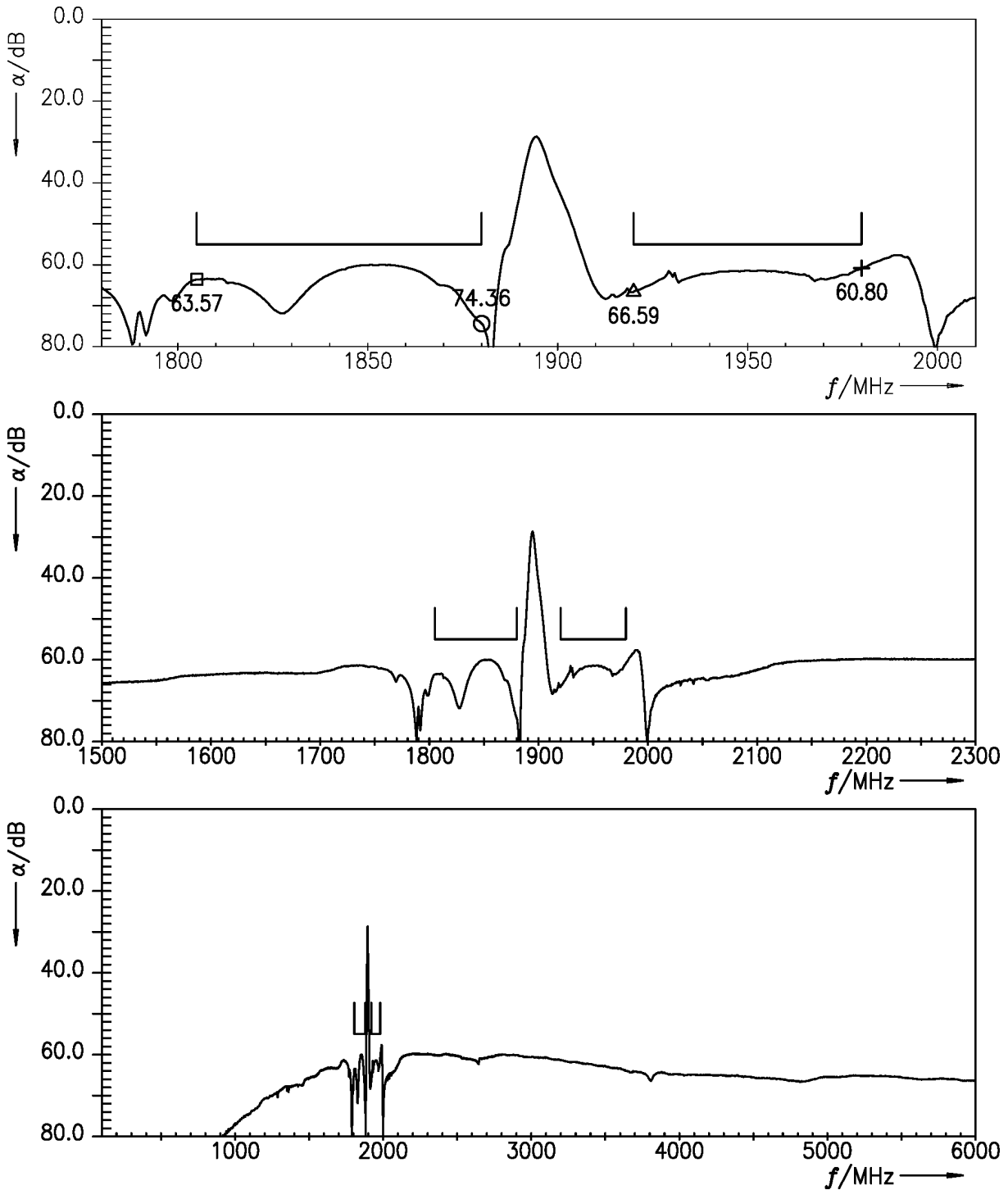


Figure 24: Cross-isolation EN-DC 4G/5G n1 TX – EN-DC 4G/5G n3 RX.

23.2 EN-DC 4G/5G n1 TX – EN-DC 4G/5G n7 RX

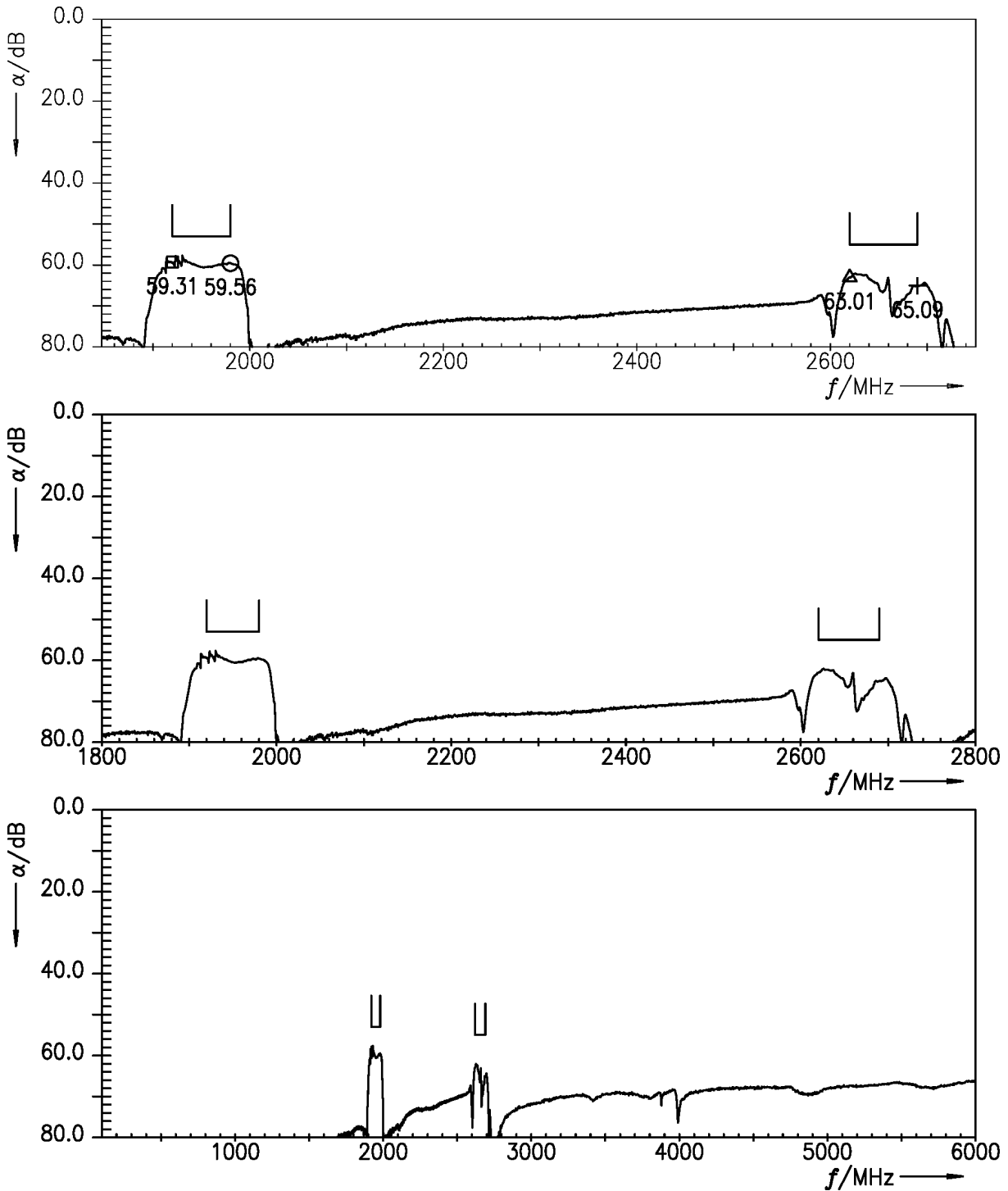


Figure 25: Cross-isolation EN-DC 4G/5G n1 TX – EN-DC 4G/5G n7 RX.

23.3 EN-DC 4G/5G n1 TX – EN-DC 4G/5G n66 RX

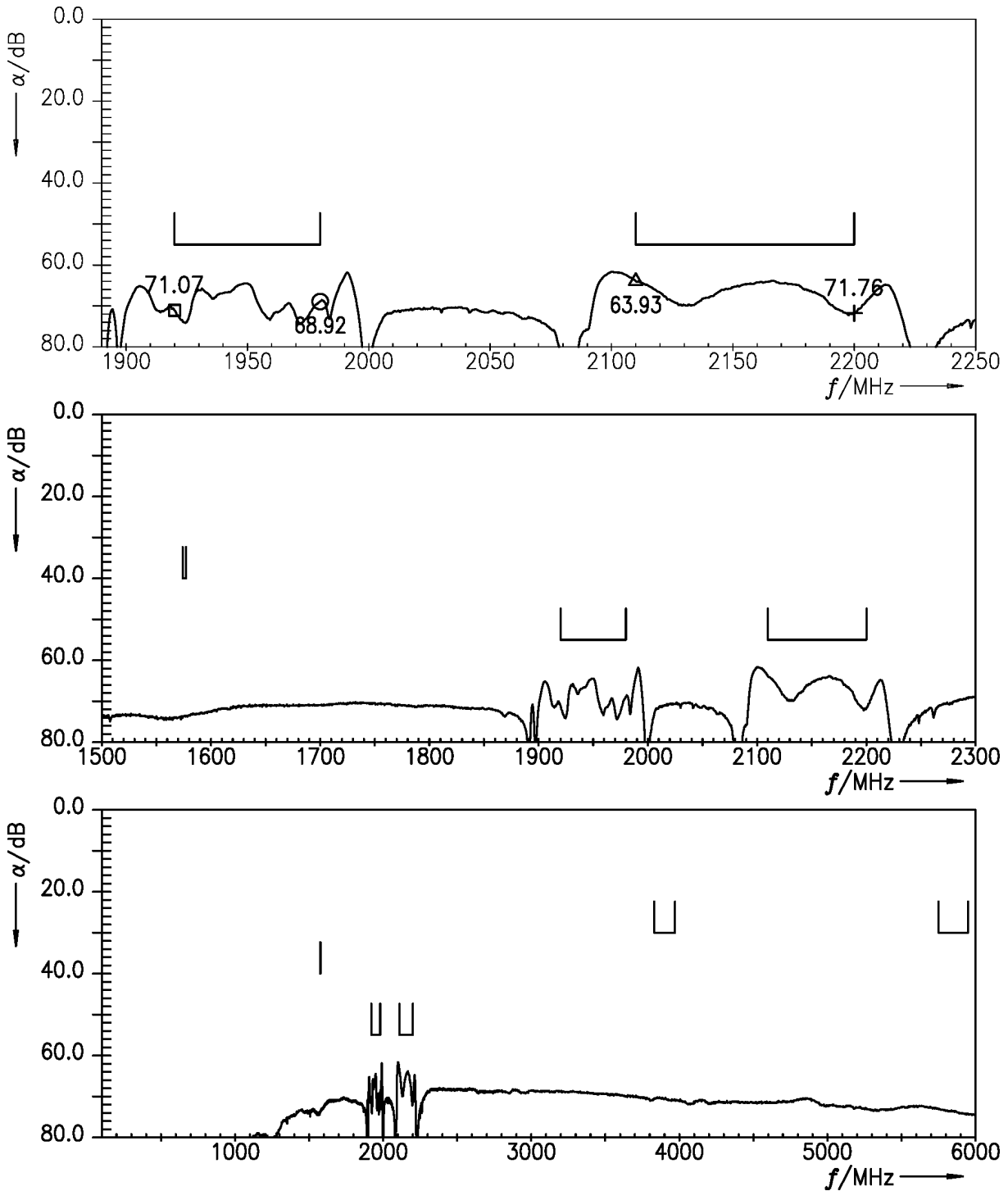


Figure 26: Cross-isolation EN-DC 4G/5G n1 TX – EN-DC 4G/5G n66 RX.

23.4 EN-DC 4G/5G n3 TX – EN-DC 4G/5G n7 RX

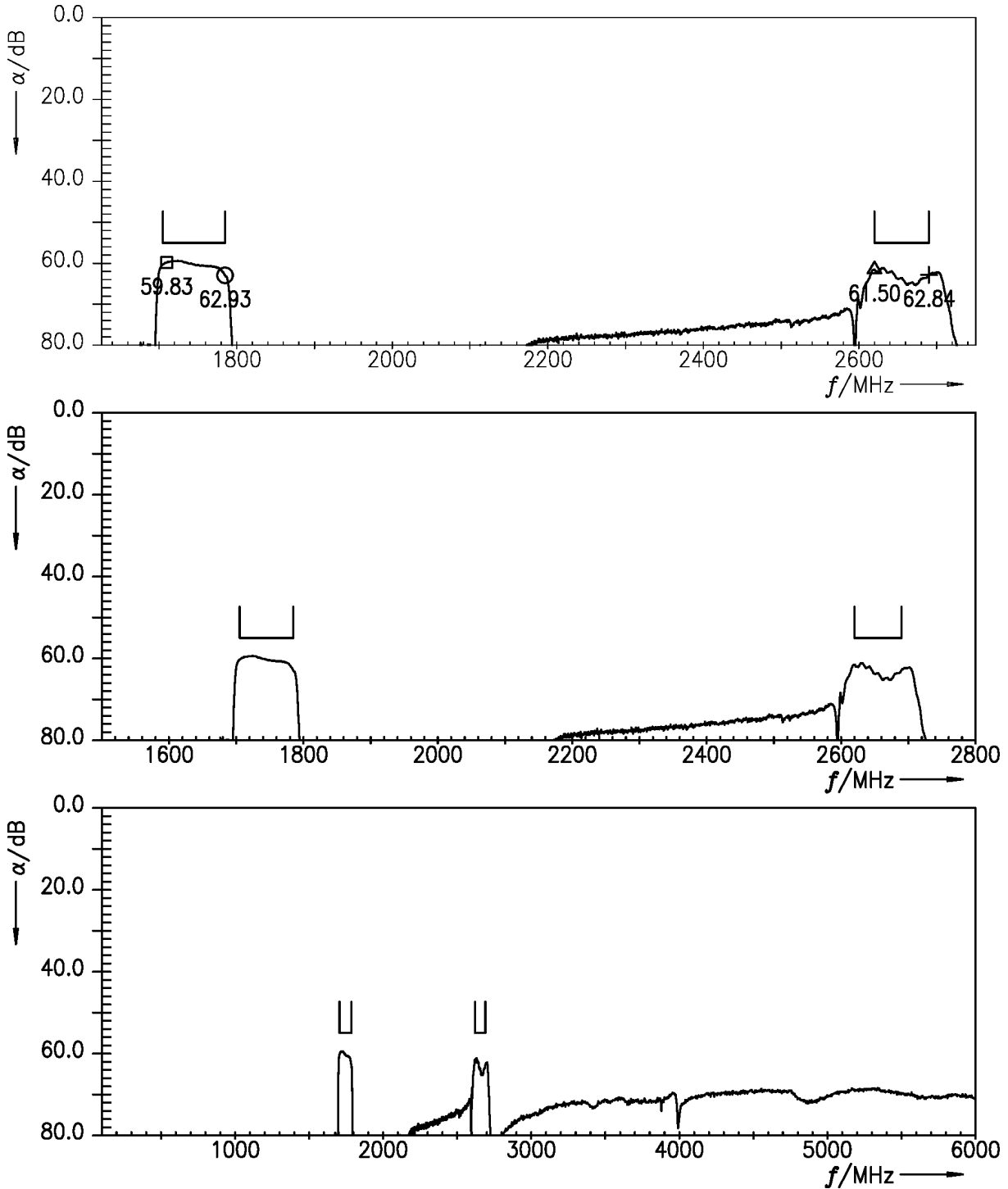


Figure 27: Cross-isolation EN-DC 4G/5G n3 TX – EN-DC 4G/5G n7 RX.

23.5 EN-DC 4G/5G n3 TX – EN-DC 4G/5G n66 RX

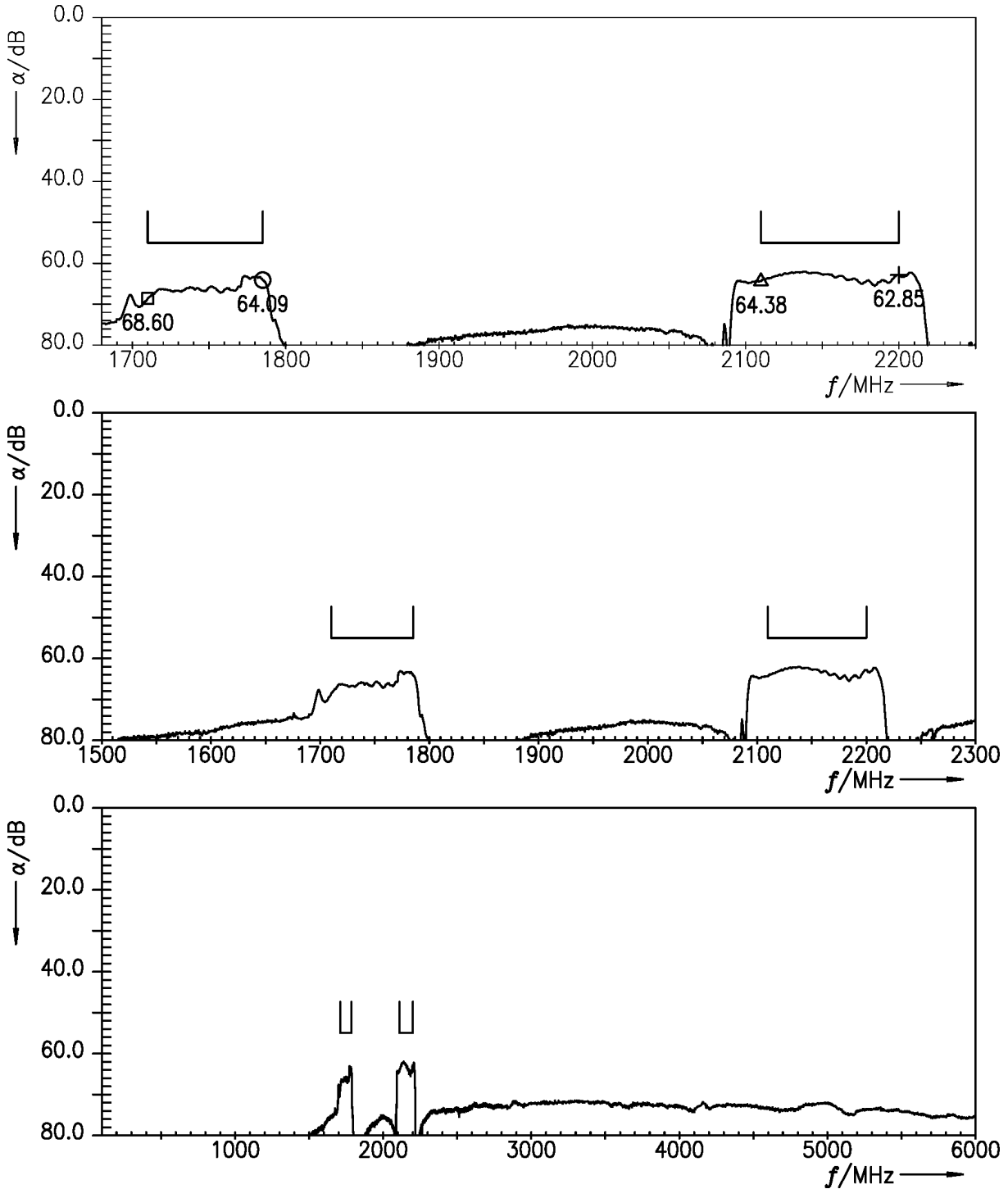


Figure 28: Cross-isolation EN-DC 4G/5G n3 TX – EN-DC 4G/5G n66 RX.

23.6 EN-DC 4G/5G n7 TX – EN-DC 4G/5G n3 RX

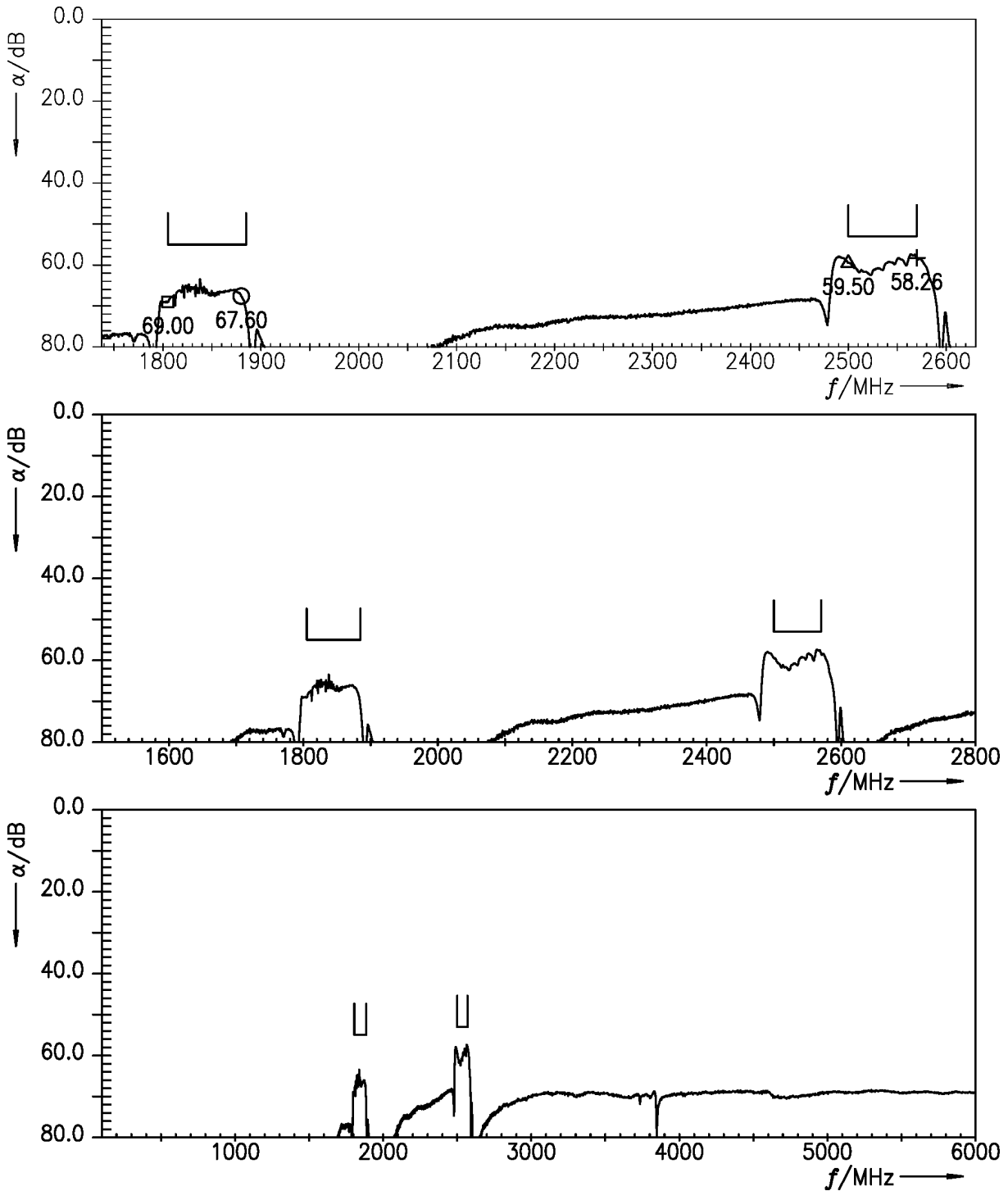


Figure 29: Cross-isolation EN-DC 4G/5G n7 TX – EN-DC 4G/5G n3 RX.

23.7 EN-DC 4G/5G n7 TX – EN-DC 4G/5G n66 RX

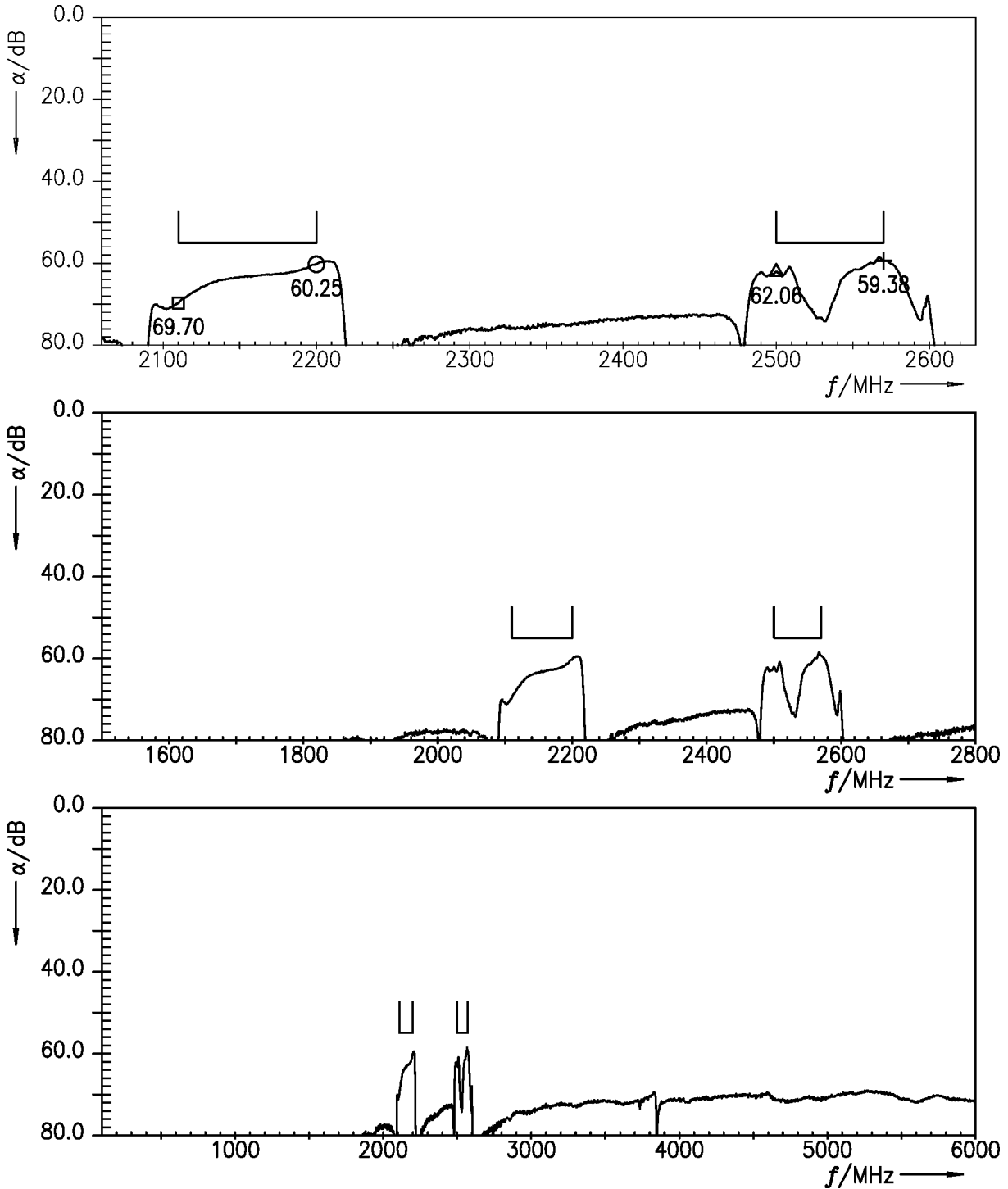


Figure 30: Cross-isolation EN-DC 4G/5G n7 TX – EN-DC 4G/5G n66 RX.

24 Packing material

24.1 Tape

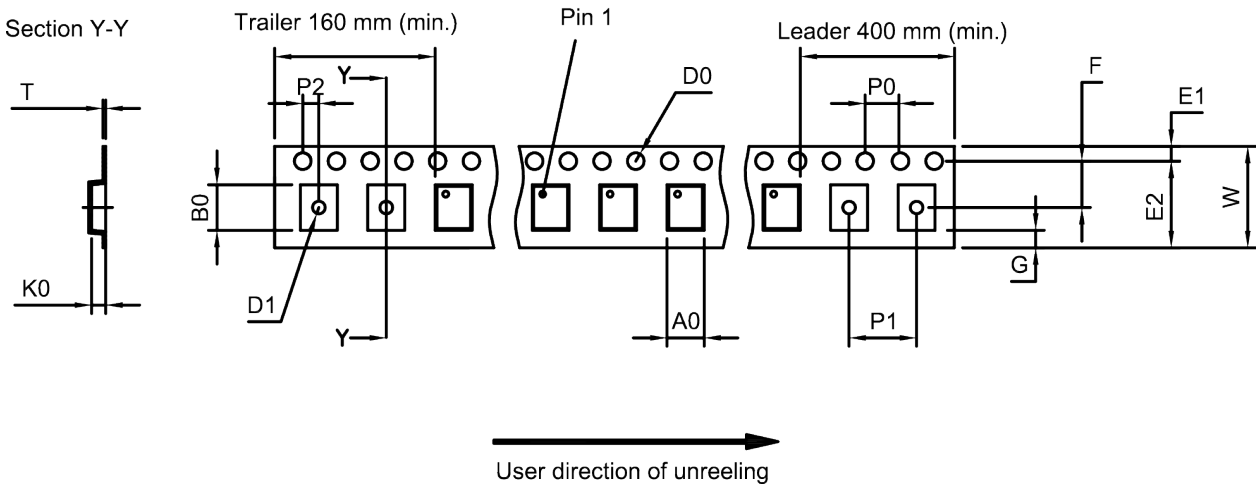


Figure 31: Drawing of tape (first-angle projection) for illustration only and not to scale. The valid tape dimensions are listed in Table 1.

A ₀	2.25±0.05 mm	E ₂	10.25+0.2/-0 mm	P ₁	4.0±0.1 mm
B ₀	2.75±0.05 mm	F	5.5±0.05 mm	P ₂	2.0±0.05 mm
D ₀	1.5+0.1/-0 mm	G	0.75 mm (min.)	T	0.3±0.03 mm
D ₁	1.5 mm (min.)	K ₀	0.84±0.1 mm	W	12.0+0.3/-0.1 mm
E ₁	1.75±0.1 mm	P ₀	4.0±0.1 mm		

Table 1: Tape dimensions.

24.2 Reel with diameter of 180 mm

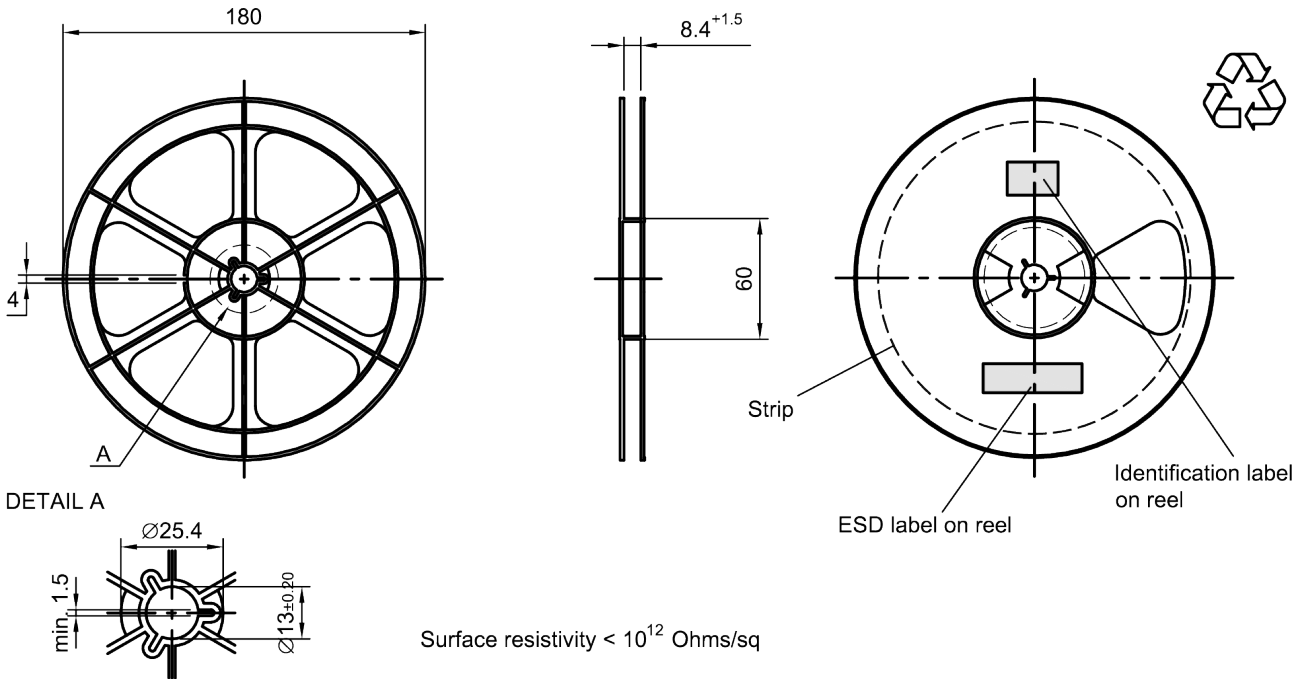


Figure 32: Drawing of reel (first-angle projection) with diameter of 180 mm.

Dimensions [mm]

X = 220+5

Y = 235+5

Sealing area 10±3

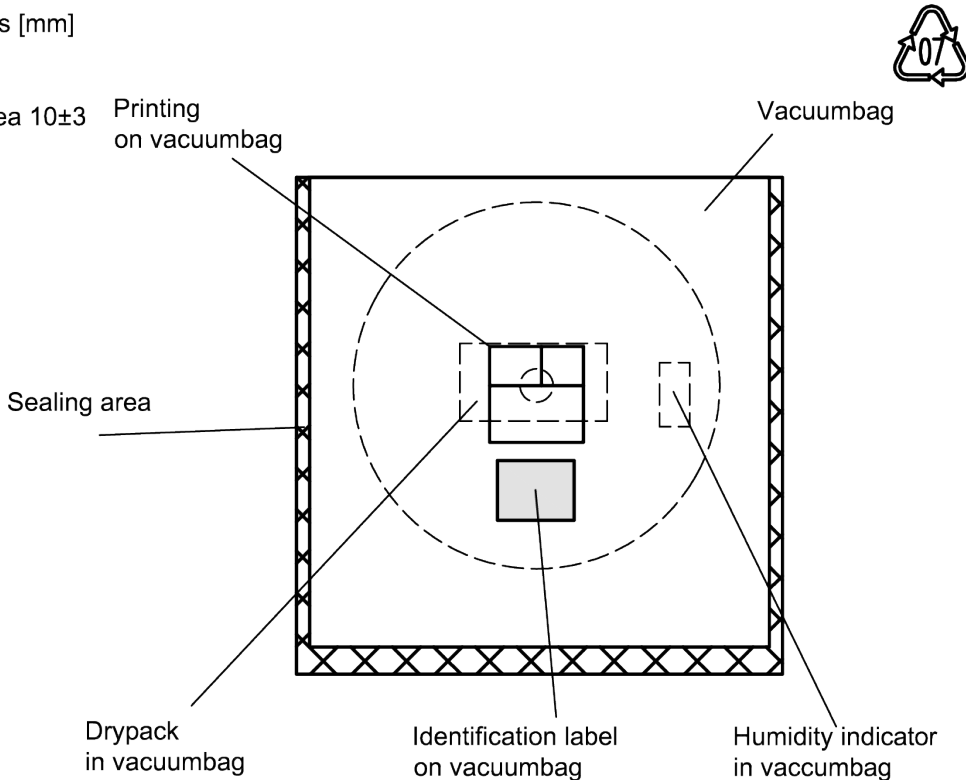


Figure 33: Drawing of moisture barrier bag (MBB) for reel with diameter of 180 mm.

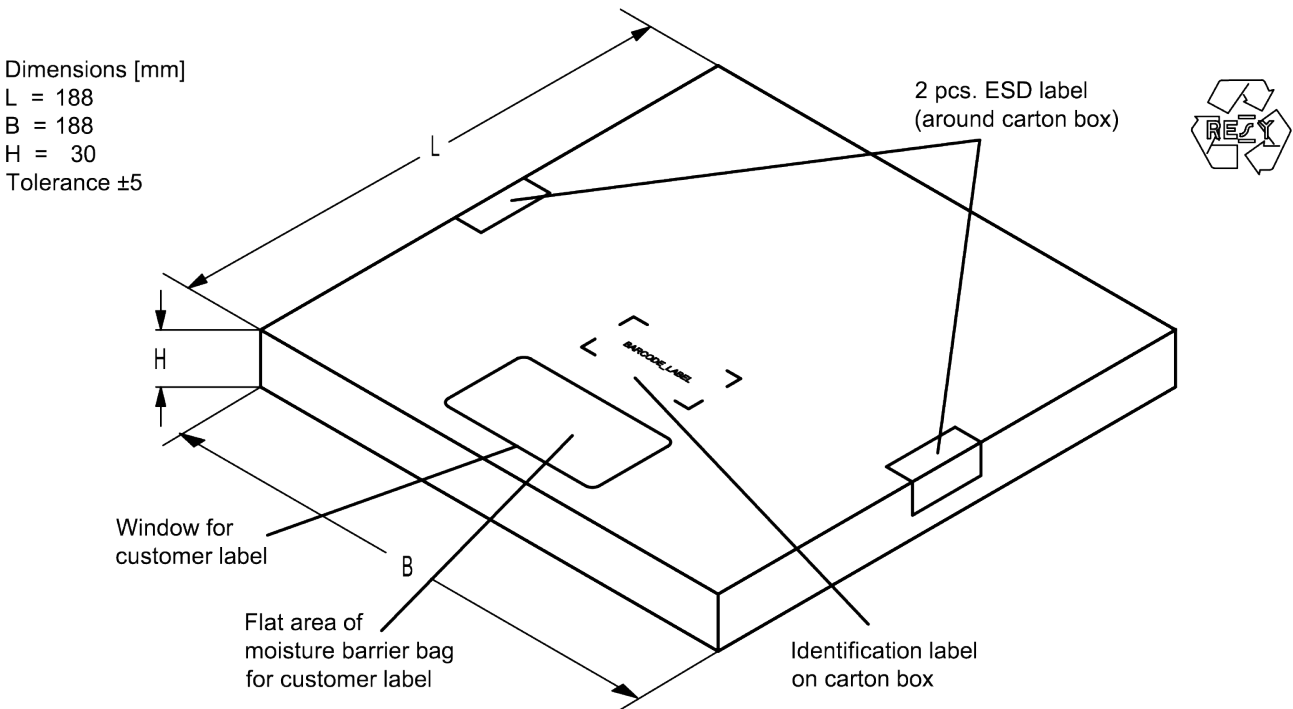


Figure 34: Drawing of folding box for reel with diameter of 180 mm.

24.3 Reel with diameter of 330 mm

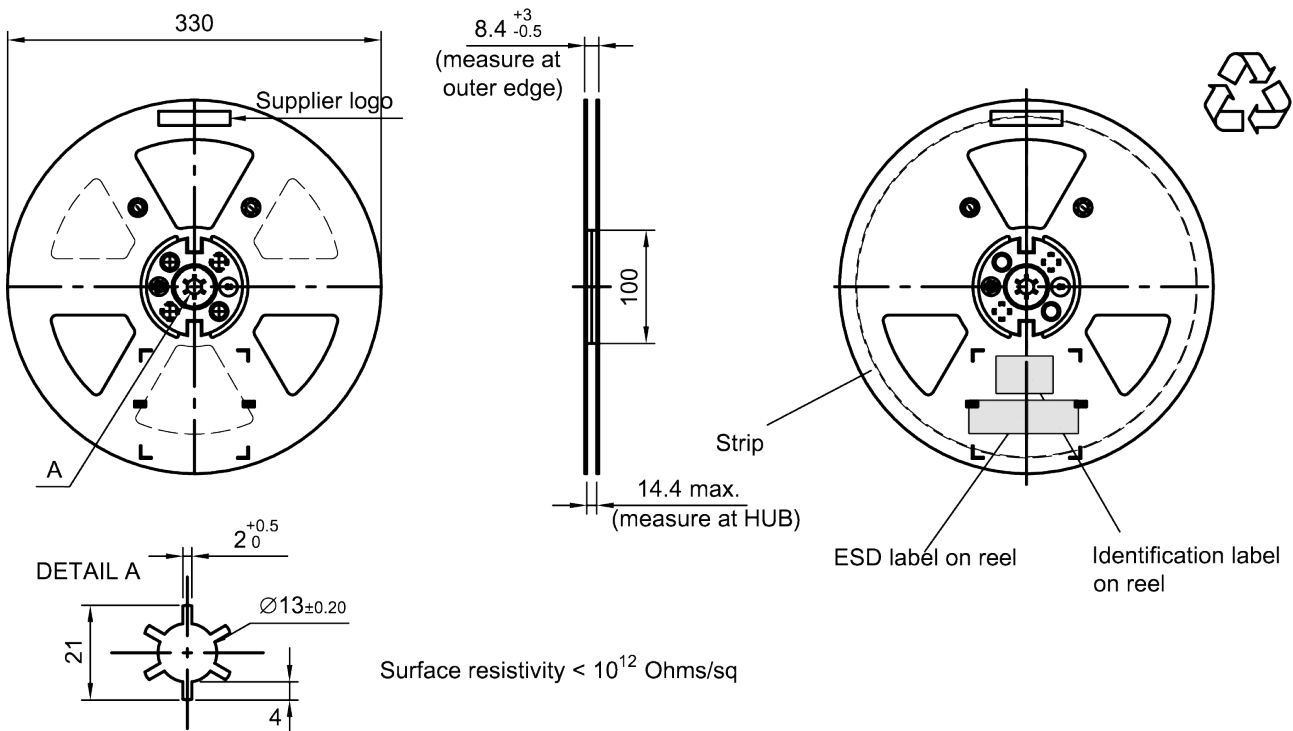


Figure 35: Drawing of reel (first-angle projection) with diameter of 330 mm.

Dimensions [mm]

X = 400+5

Y = 418+5

Sealing area 10±3

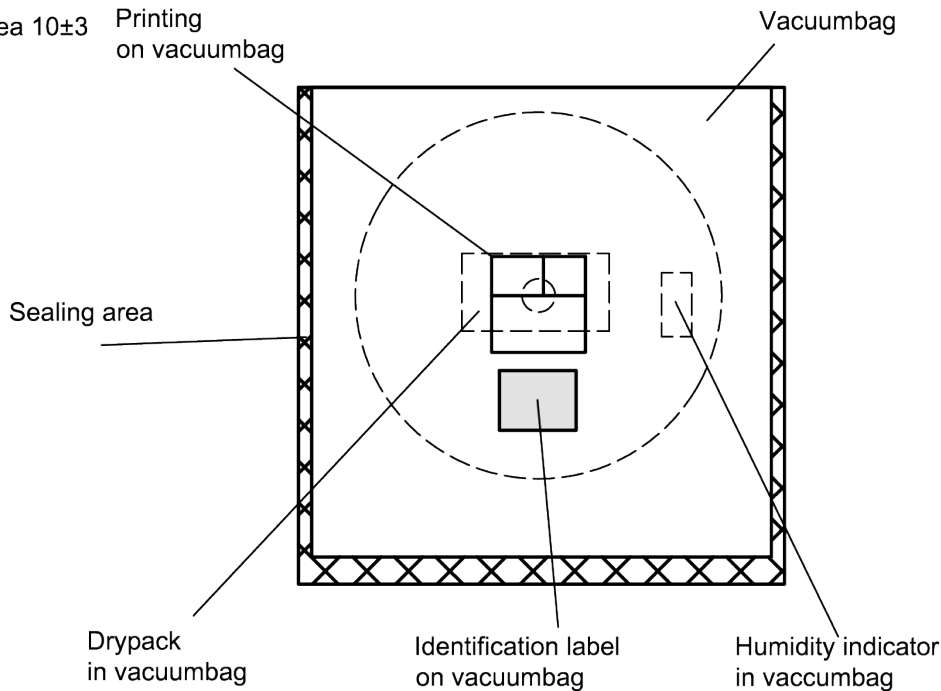


Figure 36: Drawing of moisture barrier bag (MBB) for reel with diameter of 330 mm.

Dimensions [mm]

L = 335

B = 338

H = 36 (for 8 mm tape width)

40 (for 12 mm tape width)

Tolerance ±5

2 pcs. ESD label
(around carton box)

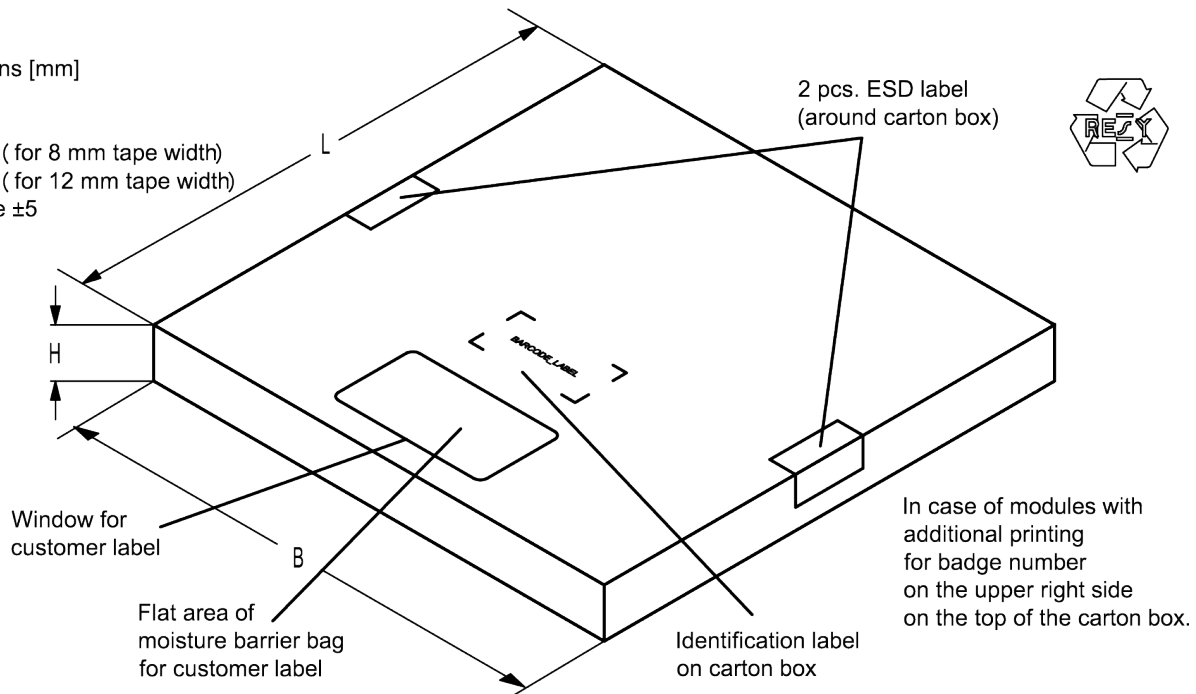


Figure 37: Drawing of folding box for reel with diameter of 330 mm.

25 Marking

Products are marked with product type number and lot number encoded according to Table 2:

■ Type number:

The 4 digit type number of the ordering code, e.g., B3xxxxB**1234**xxxx,
is encoded by a special BASE32 code into a 3 digit marking.

Example of decoding type number marking on device in decimal code.
16J => **1234**
 $1 \times 32^2 + 6 \times 32^1 + 18 (=J) \times 32^0 =$ **1234**

The BASE32 code for product type M5009 is 4WH.

■ Lot number:

The last 5 digits of the lot number, e.g., **12345**,
are encoded based on a special BASE47 code into a 3 digit marking.

Example of decoding lot number marking on device in decimal code.
5UY => **12345**
 $5 \times 47^2 + 27 (=U) \times 47^1 + 31 (=Y) \times 47^0 =$ **12345**

Adopted BASE32 code for type number			
Decimal value	Base32 code	Decimal value	Base32 code
0	0	16	G
1	1	17	H
2	2	18	J
3	3	19	K
4	4	20	M
5	5	21	N
6	6	22	P
7	7	23	Q
8	8	24	R
9	9	25	S
10	A	26	T
11	B	27	V
12	C	28	W
13	D	29	X
14	E	30	Y
15	F	31	Z

Adopted BASE47 code for lot number			
Decimal value	Base47 code	Decimal value	Base47 code
0	0	24	R
1	1	25	S
2	2	26	T
3	3	27	U
4	4	28	V
5	5	29	W
6	6	30	X
7	7	31	Y
8	8	32	Z
9	9	33	b
10	A	34	d
11	B	35	f
12	C	36	h
13	D	37	n
14	E	38	r
15	F	39	t
16	G	40	v
17	H	41	\
18	J	42	?
19	K	43	{
20	L	44	}
21	M	45	<
22	N	46	>
23	P		

Table 2: Lists for encoding and decoding of marking.

26 Soldering profile

The recommended soldering process is in accordance with IEC 60068-2-58 – 3rd edit and IPC/JEDEC J-STD-020B.

ramp rate	≤ 3 K/s
preheat	125 °C to 220 °C, 150 s to 210 s, 0.4 K/s to 1.0 K/s
$T > 220\text{ °C}$	30 s to 70 s
$T > 230\text{ °C}$	min. 10 s
$T > 245\text{ °C}$	max. 20 s
$T \geq 255\text{ °C}$	–
peak temperature T_{peak}	250 °C +0/-5 °C
wetting temperature T_{min}	230 °C +5/-0 °C for 10 s ± 1 s
cooling rate	≤ 3 K/s
soldering temperature T	measured at solder pads

Table 3: Characteristics of recommended soldering profile for lead-free solder (Sn95.5Ag3.8Cu0.7).

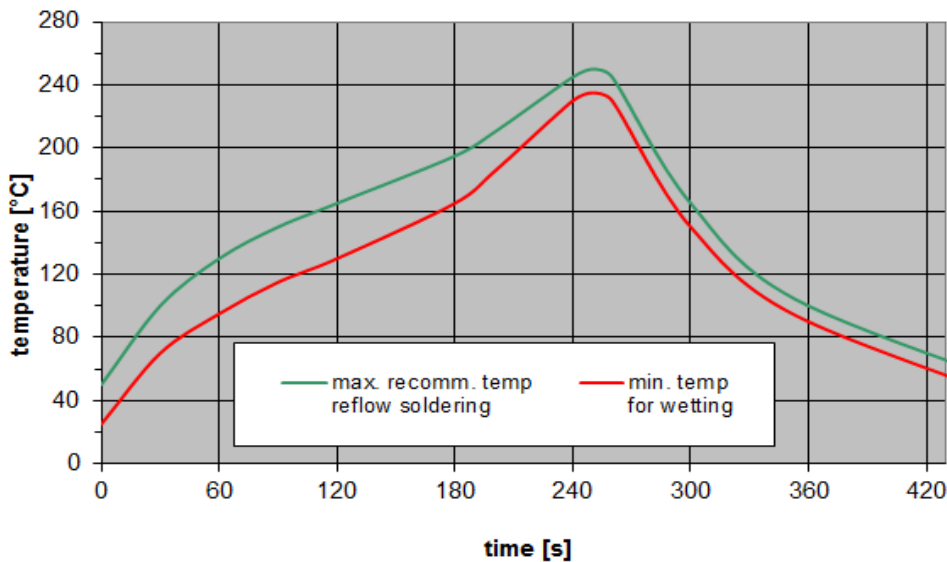


Figure 38: Recommended reflow profile for convection and infrared soldering – lead-free solder.

27 Annotations

27.1 RoHS compatibility

ROHS-compatible means that products are compatible with the requirements according to Art. 4 (substance restrictions) of Directive 2011/65/EU of the European Parliament and of the Council of June 8th, 2011, on the restriction of the use of certain hazardous substances in electrical and electronic equipment ("Directive") with due regard to the application of exemptions as per Annex III of the Directive in certain cases.

27.2 Scattering parameters (S-parameters)

The pin/port assignment is available in the headers of the S-parameter files. Please contact your local RF360 sales office.

27.3 Ordering codes / product IDs and packing units

Ordering code / product ID	RF360 label	Packing unit
B39272M5009D310W 1	B39272-M5009-D310-W01	10000 pcs

Table 4: Ordering codes / product IDs and packing units.

28 Cautions and warnings

28.1 Display of ordering codes for RF360 products

The ordering code for one and the same product can be represented differently in data sheets, data books, other publications and the website of RF360, or in order-related documents such as shipping notes, order confirmations and product labels. The varying representations of the ordering codes are due to different processes employed and do not affect the specifications of the respective products. Detailed information can be found on the Internet under <https://rfe.qualcomm.com/>.

28.2 Material information

Due to technical requirements components may contain dangerous substances. For information on the type in question please also contact one of our sales offices.

For information on recycling of tapes and reels please contact one of our sales offices.

28.3 Moldability

Before using in overmolding environment, please contact your local RF360 sales office.

28.4 Package information

Landing area

The printed circuit board (PCB) land pattern (landing area) shown is based on RF360 internal development and empirical data and illustrated for example purposes, only. As customers' SMD assembly processes may have a plenty of variants and influence factors which are not under control or knowledge of RF360, additional careful process development on customer side is necessary and strongly recommended in order to achieve best soldering results tailored to the particular customer needs.

Dimensions

Unless otherwise specified all dimensions are understood using unit millimeter (mm).

Projection method

Unless otherwise specified first-angle projection is applied.

29 Important notes

The following applies to all products named in this publication:

1. Some parts of this publication contain **statements about the suitability of our products for certain areas of application**. These statements are based on our knowledge of typical requirements that are often placed on our products in the areas of application concerned. We nevertheless expressly point out **that such statements cannot be regarded as binding statements about the suitability of our products for a particular customer application**. As a rule, RF360 Europe GmbH and its affiliates are either unfamiliar with individual customer applications or less familiar with them than the customers themselves. For these reasons, it is always ultimately incumbent on the customer to check and decide whether an RF360 product with the properties described in the product specification is suitable for use in a particular customer application.
2. We also point out that **in individual cases, a malfunction of electronic components or failure before the end of their usual service life cannot be completely ruled out in the current state of the art, even if they are operated as specified**. In customer applications requiring a very high level of operational safety and especially in customer applications in which the malfunction or failure of an electronic component could endanger human life or health (e.g. in accident prevention or life-saving systems), it must therefore be ensured by means of suitable design of the customer application or other action taken by the customer (e.g. installation of protective circuitry or redundancy) that no injury or damage is sustained by third parties in the event of malfunction or failure of an electronic component.
3. **The warnings, cautions and product-specific notes must be observed.**
4. In order to satisfy certain technical requirements, **some of the products described in this publication may contain substances subject to restrictions in certain jurisdictions (e.g. because they are classed as hazardous)**. Useful information on this will be found in our Material Data Sheets on the Internet (<https://rfe.qualcomm.com>). Should you have any more detailed questions, please contact our sales offices.
5. We constantly strive to improve our products. Consequently, **the products described in this publication may change from time to time**. The same is true of the corresponding product specifications. Please check therefore to what extent product descriptions and specifications contained in this publication are still applicable before or when you place an order. We also **reserve the right to discontinue production and delivery of products**. Consequently, we cannot guarantee that all products named in this publication will always be available.
The aforementioned does not apply in the case of individual agreements deviating from the foregoing for customer-specific products.

单击下面可查看定价，库存，交付和生命周期等信息

[>>Qualcomm-RF360](#)